## BULK DC-DC CONVERSION FOR MVDC APPLICATIONS

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## INTRODUCTION

Power Electronics Laboratory at EPFL

## INSTRUCTORS



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| :--- | :--- |
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| 2002 | Dipl. Ing., University of Novi Sad, Novi Sad, Serbia |

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2021 M.Sc., Universidade Federal de Santa Catarina (UFSC), Florianópolis, Brasil

## POWER ELECTRONICS LABORATORY AT EPFL



- Online since February 2014
- Currently: 10 PhD students, 4 Post Docs, 1 Administrative Assistant
- Funding CH: SNSF, SFOE, Innosuisse
- Funding EU: H2020, S2R JU, ERC CoG
- Funding Industry: OEMs
-https://www.epfl.ch/labs/pel/


Competence Centre


[^0]
## RESEARCH FOCUS

## MVDC Technologies and Systems

- System Stability
- Protection Coordination
- Power Electronic Converters

ENERGY CONVERSION TECHNOLOGIES AND SYSTEMS


High Power Electronics

- Multilevel Converters
- Solid State Transformers
- Medium Frequency Conversion



## Components

- Semiconductor devices
- Magnetics
- Modeling, Characterization




## SCHEDULE - BEFORE LUNCH

## Before the coffee break

## 1) Introduction

- MVDC Applications
- Motivation and Challenges
- Power Electronics Converters

2) Bulk vs Modular Power Conversion

- High Power DC-DC Conversion
- Modular DC-DC Conversion
- Bulk DC-DC Conversion - DC Transformer

3) Resonant Conversion

- Resonant DC-DC Converters
- Modeling
- Control Principles


## After the coffee break

4) HV Semiconductors

- High Voltage Devices
- IGBT versus IGCT
- Design with IGCTs

5) Gate Drivers for IGCT

- Operating Principles
- Optimization for the Resonant Operation
- High Frequency Operation

6) IGCT Resonant Switching

- ZVS versus ZCS
- Series-connection of IGCTs
- High Frequency Operation

Tutorial pdf can be downloaded from: (Source: https://www.epfl.ch/labs/pel/publications-2/publications-talks/)

## SCHEDULE - AFTER LUNCH

## Before the coffee break

7) MFT Design Challenges

- MW Design Challenges
- Technologies and Materials
- Electrical and Thermal Modeling

8) MFT Design Examples

- MFTs for SST
- MFTs for Bulk Power
- Special Designs

9) MFT Design Optimization

- Design Optimization
- Practical 1MW 5kHz Design Experience
- Experimental Results



## After the coffee break

10) MVDC Power Distribution Networks

- MVDC Network Modelling
- DC Transformer in MVDC Power Distribution Networks
- Operational Performance Assessment

11) Direct Current Transformer Features

- Operating Principles
- Power Reversal Methods
- Practical Examples

12) Summary and Conclusions

- Why MVDC?
- How MVDC?
- When MVDC?

Tutorial pdf can be downloaded from: (Source: https://www.epfl.ch/labs/pel/publications-2/publications-talks/)

# INTRODUCTION 

MVDC Applications, Systems and Technologies

## WHY DC?

- No reactive power

- No constraints imposed upon transmission distance
- Transmission capacity increase
- Lower transmission losses
- Alleviated stability problems
- No skin effect $\left(R_{Y} \downarrow \Rightarrow P_{Y} \uparrow\right)$
- Cheaper solution ("Break-even distance")
- Underwater cable transmission
- No need for synchronization (Marine applications)
- Direct integration of Renewable Energy Sources
- Challenges $\Rightarrow$ DC Transformer/Protection?

- Cost comparison between AC and DC systems

- High voltage cable

[1] Uzair Javaid et al. "MVDC supply technologies for marine electrical distribution systems." CPSS Transactions on Power Electronics and Applications 3.1 (2018), pp. 65-76


## CONVERSION OF AC LINES INTO DC

- Transmission capacity increase
- Employment of the existing conductors
- No change in tower foundations
- Possible tower head adjustment
- Possible isolator assemblies adjustment


ム Angle DC Project - UK


- Conversion of two typical AC lines into DC [2], [3], [4], [5]


## MVDC POWER DISTRIBUTION NETWORKS

## MVDC Power Distribution Networks

- Feasibility (Applications)
- System Level Gains
- Dynamic Stability
- Passive and Stable
- Flexible, Modular and Scalable
- Efficient


## Protection

- DC Breaker?
- Fault Current Limiting by Converters
- Protection Coordination



## A TREND TOWARDS DC

## Bulk power transmission

- Break even distance against AC lines
- ~ 50-100 km for subsea cables or 600 km for overhead lines
- Long history since 1950s
- Interconnection of asynchronous grids

- From mercury arc rectifiers to modern HVDC systems


## LVDC ships

- Variable frequency generators $\Rightarrow$ maximum efficiency of the internal combustion engines
- Commercial products by ABB \& Siemens

- Specialized vessels with LVDC distribution


## Datacenters

- $380 \mathrm{~V}_{\mathrm{dc}}$
- DC loads (including UPS)
- Expected efficiency increase


## Large PV powerplants

- $1500 \mathrm{~V}_{\mathrm{dc}}$ PV central inverters
- Higher number of series-connected panels per string


A 1500 V PV inverter - step towards the MVDC

## Open challenges

- DC breaker
- Conversion blocks missing
- Protection coordination
- Business case


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- Business case

DC is beneficial for medium / high power applications

- Specialized vessels with LVDC distribution


## EMERGING MVDC APPLICATIONS

## Installations

- ABB HVDC Light demo: $4.3 \mathrm{~km} / \pm 9 \mathrm{kV} \mathrm{dc}_{\text {c }}$ [6]
- Tidal power connection: $16 \mathrm{~km} / 10 \mathrm{kV}$ dc (based on MV3000 \& MV7000) [7]

- Unidirectional oil platform connection in China: $29.2 \mathrm{~km} / \pm 15 \mathrm{kV}_{\mathrm{dc}}$ [8]


## Projects

- Angle DC: conversion of 33 kV MVac line to $\pm 27 \mathrm{kV}$ MVdc [9]


## Universities

- Increased number of laboratories active in high power domain
- China, Europe, USA,...


## Products

- Siemens MVDC Plus
- $30-150 \mathrm{MW}$
- < 200 km
- $< \pm 50 \mathrm{kV}$ dc

- RXPE Smart VSC-MVDC
- 1-10 MVAr
- $\pm 5- \pm 50 \mathrm{kV}_{\mathrm{dc}}$
- $40-200 \mathrm{~km}$


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## A TREND TOWARDS HIGHLY MODULAR CONVERTER TOPOLOGIES

## HVDC

- Decoupled semiconductor switching frequency from the converter apparent switching frequency
- Improved harmonic performance $\Rightarrow$ less / no filters
- Series-connection of semiconductors still possible
- Fault blocking capability depending on the cell type



## Solid-state transformers (SSTs)

- Power density increase w/ conversion \& isolation at higher frequency
- Grid applications / traction transformer w/ different optimization objectives
- MFT design / isolation are the bottlenecks



## MV drives

- Monolithic ML topologies (NPC, NPP, FC, ANPC) are not scalable
- Robicon drive $\rightarrow$ everyone offers it
- Siemens \& Benshaw: MMC drive
- Low dv/dt $\rightarrow$ motor friendly


FACTS

- SFC for railway interties (direct catenary connection)
- STATCOM
- BESS (split batteries)



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FACTS

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- STATCOM
- BESS (split batteries)
$\Rightarrow$ Modularity provides obvious benefits in high power AC-DC applications!



## SOLID STATE TRANSFORMER FOR TRACTION (ABB - 1.2MW PETT)

## Characteristics

- 1-Phase MVAC to MVDC
- Power: 1.2MVA
- Input AC voltage: $15 \mathrm{kV}, 16.7 \mathrm{~Hz}$
- Output DC voltage: 1500 V
- 9 cascaded stages $(\mathrm{n}+1)$
- input-series output-parallel
- double stage conversion


## 99 Semiconductor Devices

- HV PEBB: $9 \times(6 \times 6.5 \mathrm{kV}$ IGBT $)$
- LV PEBB: $9 \times(2 \times 3.3 \mathrm{kV}$ IGBT $)$
- Bypass: $9 \times(2 \times 6.5 \mathrm{kV}$ IGBT)
- Decoupling: $9 \times(1 \times 3.3 \mathrm{kV}$ Diode)


## 9 MFTs

- Power: 150kW
- Frequency: 1.75 kHz
- Core: Nanocrystalline
- Winding: Litz
- Insulation / Cooling: Oil

$\Delta$ ABB PETT scheme [10], [11]


## SOLID STATE TRANSFORMER FOR TRACTION - DESIGN

## Retrofitted to shunting locomotive

- Replaced LFT + SCR rectifier
- Propulsion motor - 450kW
- 12 months of field service
- No power electronic failures
- Efficiency around $96 \%$
- Weight: $\approx 4.5 \mathrm{t}$


## Technologies

- Standard 3.3 kV and 6.5 kV IGBTs
- De-ionized water cooling
- Oil cooling/insulation for MFTs
- $\mathrm{n}+1$ redundancy
- IGBT used for bypass switch


## Displayed at:

- Swiss Museum of Transport
- https://www.verkehrshaus.ch

[10] D. Dujic et al. "Power Electronic Traction Transformer-Low Voltage Prototype." IEEE Transactions on Power Electronics 28.12 (Dec. 2013), pp. 5522-5534
11] C. Zhao et al. "Power Electronic Traction Transformer-Medium Voltage Prototype." IEEE Transactions on Industrial Electronics 61.7 (July 2014), pp. 3257-3268


## SOLID-STATE TRANSFORMER - OTHER EXAMPLES

## UNIFLEX-PM

- Reduced scale prototypes

- UNIFLEX-PM prototype

GE

- Full scale prototype

- GE prototype [12]

FREEDM

- Reduced scale prototypes


## HEART

- Reduced scale prototypes

- FREEDM SSTs [13]

HUST

- Full scale prototype

- HUST SST [14]

- HEART project

XD Electric Company

- Full scale prototype

$\Delta$ XD Electric Company SST [15]


## SOLID-STATE TRANSFORMER (SST)

## Concept and motivation?

- SST = Switching stages + Isolation
- Firstly envisioned within AC grids
- Power Electronic Building Blocks (PEBBs)
- Conventional transformer vs SST?
- Operating frequency increase (MFT)

|  | Grid Tx | SST |
| :--- | :---: | :---: |
| Controlability | No | Yes |
| Efficiency | $\eta \geq 99 \%$ | $P_{?}$ |
| Q compensation | No | Yes |
| Fault tolerance | No | Yes |
| Size | Bulky | Compact |
| Cost | Low | High |

Advantages at the expense of cost and reduced efficiency!


- Conventional AC grid transformer


A Solid-State Transformer employed with the aim of interfacing two AC systems [16], [17]

## DC-DC CONVERTERS

- Inherent part of the almost all SST topologies
- Expansion of the existing power system
- Enabling technology for MVDC
- Penetration of renewable energy sources
- Fast / Ultra Fast EV charging
- Medium Frequency conversion

- Employment of a DC-DC SST within RES-based systems

- Concept of a modern power system

- Fast EV charging concept


## MEDIUM FREQUENCY TRANSFORMER (MFT) CHALLENGES

- Skin and proximity effect losses: impact on efficiency and heating
- Cooling: increase of power density $\Rightarrow$ decrease in size $\Rightarrow$ less cooling surface $\Rightarrow$ higher $R_{\text {th }} \Rightarrow$ higher temperature gradients
- Non-sinusoidal excitation: impact on core and winding losses and insulation
- Insulation: coordination and testing taking into account high $\frac{d V}{d t}$ characteristic for power electronic converters
- Accurate electric parameter control: especially in case of resonant converter applications

- Medium Frequency Transformer challengesMFT design is generally challenging and requires multiphysics considerations and multiobjective optimization


## MFT NONSINUSOIDAL POWER ELECTRONIC WAVEFORMS

## DAB Converter:




- $V_{1,2}$ square
- I non-sinusoidal


## Series Resonant Converter:




- $V_{1,2}$ square
- I sinusoidal


## Core Losses:



- Data-sheet - sinusoidal excitation
- Steinmetz - sinusoidal excitation losses
- Core is excited with square pulses!
- Losses must be correctly evaluated
- Generalization of Steinmetz model
- Specific AC core losses

Winding Losses:


- Current waveform impacts the winding losses
- Copper is a linear material
- Losses can be evaluated in harmonic basis
- Current harmonic content must be evaluated
- Losses are the sum of the individual harmonic losses


## MFT ACCURATE PARAMETERS CONTROL

## DAB Converter:



- $V_{1,2}$ square
- I non-sinusoidal


## Series Resonant Converter:



- Leakage inductance
- Controllability of the power flow
- Higher than $L_{\sigma . \text { min }}$

$$
L_{\sigma . \min }=\frac{V_{D C 1} V_{D C 2} \varphi_{\min }\left(\pi-\varphi_{\min }\right)}{2 P_{\text {out }} \pi^{2} f_{s} n}
$$

- Magnetizing Inductance is normally high

SRC

- Leakage inductance is part of resonant circuit
- Must match the reference:

$$
L_{\sigma . r e f}=\frac{1}{\omega_{0}^{2} C_{r}}
$$

- Magnetizing inductance is normally high
- Reduced in case of LLC
- Limits the magnetization current to the reference $I_{m . r e f}$
- Limits the switch-off current and losses

$$
L_{m}=\frac{n V_{D C 2}}{4 f_{s} I_{\text {m.ref }}}
$$

- $I_{\text {m.ref }}$ has to be sufficiently high to maintain ZVS


## MFT VARIETY OF DESIGNS...



ABB: 350kW, 10kHz


IKERLAN: $400 \mathrm{~kW}, 1 \mathrm{kHz}$


STS: 450kW, 8kHz


ABB: $3 \times 150 \mathrm{~kW}, 1.8 \mathrm{kHz}$


FAU-EN: 450kW, 5.6 kHz


KTH: $170 \mathrm{~kW}, 4 \mathrm{kHz}$


BOMBARDIER: 350 kW , 8 kHz


CHALMERS: $50 \mathrm{~kW}, 5 \mathrm{kHz}$


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$


ALSTOM: 1500kW, 5kHz


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$


EPFL: $100 \mathrm{~kW}, 10 \mathrm{kHz}$


IKERLAN: 400kW, 5kHz


EPFL: 300kW, 2kHz


ACME: ???kW, ???kHz

## EMPOWER - A EUROPEAN RESEARCH COUNCIL CONSOLIDATOR GRANT

- EMPOWER-ing the future energy systems

MVDC Grids
DC-DC Conversion
DC Protection

- DC Transformer
- Resonant principles
- HV semiconductors
- Flexibility
- Medium frequency conversion
- Active protection

- Today's AC and tomorrow's DC power distribution networks enabled by DC Transformers
^ The EMPOWER - Holistic and Integrated


## EMPOWER - A EUROPEAN RESEARCH COUNCIL CONSOLIDATOR GRANT



- Today's AC and tomorrow's DC power distribution networks enabled by DC Transformers
- The EMPOWER - Holistic and Integrated

Can we make a simple DC Transfomer behaving as much as possible as equivalent AC transformer?

## BULK VS. MODULAR POWER CONVERSION

The same conversion function, but many implementation differences

## DC-DC SST - BASIC CONCEPTS

## Fractional power processing

- Multiple MFTs
- Equal power distribution among PEBBs
- MFT isolation?
- Various PEBB configurations

- Different structures employed depending upon the voltage level


## Bulk power processing

- Single MFT
- Isolation solved only once
- Various configurations/operating principles



## DC-DC SST - BASIC CONCEPTS

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- ISOP Structure

- Bulk power processing concept

Both design approaches are valid, and have their pros and cons! Many factors should be considered!

## COMMON PEBB CONFIGURATIONS

## Dual-Active Bridge



- Dual Active Bridge [18]


## Resonant Converters



$$
\begin{array}{ll}
C_{R} \quad L_{\gamma} & \begin{array}{l}
f_{r 1}=\frac{1}{2 \pi \sqrt{C_{R} L_{\gamma}}} \\
v_{A}
\end{array} \\
i_{r 2}=\frac{1}{2 \pi \sqrt{C_{R}\left(L_{\gamma}+L_{m}\right)}} \\
Q=Q\left(R_{a c}\right) \\
G=G\left(\frac{f_{s w}}{f_{r 1}}, \frac{L_{m}}{L_{\gamma}}, Q\right)
\end{array}
$$

- LLC Resonant Converter


## 1-PHASE DAB

Basic operating principles

## SINGLE-PHASE (1PH) DUAL ACTIVE BRIDGE (DAB)


Power equation

$$
\begin{aligned}
P & =\frac{1}{T} \int_{0}^{T} V_{A B} i_{T} d t \\
& =m_{T} \frac{V_{i n} V_{0}}{\omega L_{\Sigma}} \varphi\left(1-\frac{|\varphi|}{\pi}\right)
\end{aligned}
$$

## SINGLE-PHASE (1PH) DUAL ACTIVE BRIDGE (DAB)





- 1PH-DAB with its relevant waveforms


## SINGLE-PHASE (1PH) DUAL ACTIVE BRIDGE (DAB)






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Switching cycle


## SINGLE-PHASE (1PH) DUAL ACTIVE BRIDGE (DAB)





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\end{aligned}
$$

## Switching cycle



## Main features

- Phase-Modulated converter
- Simple power flow control
- Soft-switching capability
- Many other advanced modulation schemes are known


## 3-PHASE DAB

Somewhat more complicated..

## THREE-PHASE (3PH) DAB




$$
v_{a n}=\frac{2 v_{s a}-v_{s b}-v_{s c}}{3}
$$

$v_{p a}=m_{T} \frac{2 v_{s a}^{\prime}-v_{s b}^{\prime}-v_{s c}^{\prime}}{3}$


- 3PH-DAB with its relevant waveforms


## Power Equation

$$
\begin{aligned}
P & =\frac{3}{T} \int_{0}^{T} v_{a n} i_{a n} d t \\
& =m_{T} \frac{4}{3} \frac{V_{i n} V_{0}}{\omega L_{\Sigma}} \varphi\left(\frac{1}{2}-\frac{3|\varphi|}{8 \pi}\right)
\end{aligned}
$$

1-PH vs 3-PH DAB


## THREE-PHASE (3PH) DAB




$$
v_{a n}=\frac{2 v_{s a}-v_{s b}-v_{s c}}{3}
$$

$v_{p a}=m_{T} \frac{2 v_{s a}^{\prime}-v_{s b}^{\prime}-v_{s c}^{\prime}}{3}$


- 3PH-DAB with its relevant waveforms


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\end{aligned}
$$

1-PH vs 3-PH DAB


3PH-DAB is considered favorable!

## 3PH-DAB CONTROL



- Observed DAB-based system

Assuming $P_{\text {in }}=P_{\text {out }}$ :

$$
\begin{aligned}
& y_{0} i_{0}=\frac{4 m_{T} V_{i n} y_{0}}{3 \omega L} \varphi\left(\frac{1}{2}-\frac{3|\varphi|}{8 \pi}\right) \\
& \Rightarrow i_{0}=\frac{4 m_{T} V_{\text {in }}}{3 \omega L} \varphi\left(\frac{1}{2}-\frac{3|\varphi|}{8 \pi}\right)
\end{aligned}
$$Controlled current source behavior!

- DAB equivalent circuit seen from the controlled side


- Output voltage control loop


## ABRUPT PHASE ANGLE CHANGES? (I)

- Six step modulation
- Limited number of voltage states


$\Delta$ Either side of the 3PH-DAB

- DAB equivalent circuit
? Current shape in the $a \beta$ plane?

For $\omega t \in\left[(k-1) \frac{\pi}{3}, k \frac{\pi}{3}\right]$

$$
\begin{aligned}
& \mathbf{V}_{\mathbf{p}}=\mathbf{V}_{\mathbf{k}} \\
& \mathbf{V}_{\mathbf{s}}= \begin{cases}\mathbf{V}_{\mathbf{k}-\mathbf{1}}, & \omega t \in\left[(k-1) \frac{\pi}{3},(k-1) \frac{\pi}{3}+\varphi\right] \\
\mathbf{V}_{\mathbf{k}}, & \omega t \in\left[(k-1) \frac{\pi}{3}+\varphi, k \frac{\pi}{3}\right]\end{cases}
\end{aligned}
$$

$$
L \frac{d \mathbf{i}}{d t}=\mathbf{V}_{\mathbf{p}}-\mathbf{V}_{\mathbf{s}}
$$

$$
= \begin{cases}\hat{V} e^{j(k+1) \frac{\pi}{3}}, & \omega t \in\left[(k-1) \frac{\pi}{3},(k-1) \frac{\pi}{3}+\varphi\right] \\ 0, & \omega t \in\left[(k-1) \frac{\pi}{3}+\varphi, k \frac{\pi}{3}\right]\end{cases}
$$

$$
\mathbf{i}= \begin{cases}\mathbf{i}_{\mathbf{0}, \mathbf{k}}+\frac{\hat{V}}{L_{\Sigma}} t e^{j(k+1) \frac{\pi}{3}}, & \omega t \in\left[(k-1) \frac{\pi}{3},(k-1) \frac{\pi}{3}+\varphi\right] \\ \mathbf{i}_{\mathbf{0}, \mathbf{k}}+\frac{\hat{V}}{\omega L_{\Sigma}} \varphi e^{j(k+1) \frac{\pi}{3}}, & \omega t \in\left[(k-1) \frac{\pi}{3}+\varphi, k \frac{\pi}{3}\right]\end{cases}
$$



- DAB switching signals

ABRUPT PHASE ANGLE CHANGES? (I)

- Six step modulation
- Limited number of voltage states


© Either side of the 3PH-DAB

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- Amplitude of the change proportional to $\varphi$
- Phase change in $60^{\circ}$ stepsCurrent slides along a hexagon!

- DAB switching signals


## ABRUPT PHASE ANGLE CHANGES? (II)

## Recap

- Limited number of voltage states $V_{p}$ and $V_{s}$
- Current vector stepwise phase changes $\left(60^{\circ}\right)$
- Current vector magnitude directly proportional to phase angle
- Current vector slides along the hexagon [19], [20]


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What if the phase angle gets abruptly changed?


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- Current vector magnitude directly proportional to phase angle
- Current vector slides along the hexagon [19], [20]
?What if the phase angle gets abruptly changed?
- New current vector trajectory
- Hexagon decentralization $\Rightarrow$ Transformer currents asymmetry!


## Inverse $\alpha \beta 0$ transformation:

$$
\left[\begin{array}{l}
\text { ioff } \\
i_{b}^{\text {iff }} \\
i_{b}^{i_{b}}
\end{array}\right]=\left[\begin{array}{ccc}
1 & 0 & 1 \\
-\frac{1}{2} & \frac{\sqrt{3}}{2} & 1 \\
-\frac{1}{2} & -\frac{\sqrt{3}}{2} & 1
\end{array}\right] \cdot\left[\begin{array}{c}
i_{a, \text { hex }}^{\text {off }} \\
i_{\beta, \text { hex }}^{o p f} \\
0
\end{array}\right]
$$

Time constant $L_{\Sigma} / R_{\Sigma}$ determines asymmetric components decay!


## ABRUPT PHASE ANGLE CHANGES? (III)



- Safe way of achieving phase angle change (I)


## Applied phase angle sequence:

$\underbrace{\varphi_{1}}_{\text {Angle change! }} \Rightarrow \underbrace{\frac{e_{1}}{\frac{\varphi_{1}+\varphi_{2}}{2}} \Rightarrow \underbrace{\frac{\varphi_{1}+\varphi_{2}}{2}}_{\frac{T}{6}} \Rightarrow \underbrace{\frac{\varphi_{1}+\varphi_{2}}{2}}_{\frac{T}{6}}}_{\text {Transition time }=\frac{T}{2}} \Rightarrow \underbrace{\varphi_{2}}_{\text {Transition end }}$


- Safe way of achieving phase angle change (II)


## Applied phase angle sequence:



# MEDIUM VOLTAGE DC-DC 

Extending previously presented concepts.

## HOW TO HANDLE HIGH/MEDIUM VOLTAGES?


$\Delta$ Series connection of switches [21]

- Series connection of switches with snubbers
- Two voltage levels ( $n_{L V L}=2$ )
- Two-Level voltage waveforms

$\Delta$ Modular Multilevel Converter (MMC)
- Series connection of Submodules (SM)
- $n_{\text {LVL }}$ depending upon number of SMs
- Arbitrary voltage waveform generation

- Series connection of MMC-alike SMs
- $n_{\text {LVL }}$ depending upon number of SMs
- Quasi Two-Level (trapezoidal) voltage waveform


## MODULAR MULTILEVEL CONVERTER (MMC)

- Variety of conversion possibilities
- Variety of modulations
- Different types of submodules (SMs)
- Half-Bridge (HB)
- Full-Bridge (FB)
- Others...
- Arbitrary voltage waveform generation

$\Delta$ Modular Multilievel Converter (MMC)


Half-Bridge submodule and its allowed states


FB SM


Bypassed \#1


Inserted \#1


Bypassed \#2


Inserted \#2


Blocked

- Full-Bridge submodule and its allowed states

MMC-BASED DUAL ACTIVE BRIDGE (DAB)

- Basic operation principles are retained
- Easy to comprehend (AC equivalent)



## Challenges?

- Modulation choice (sine, square, etc ... ?)
- System design ( $N$ vs $V_{\text {grid }}$ )
- Energy balancing
- Q2L mode \& capacitors sizing
- Engagement within bipolar grids


- MMC-based 1PH-DAB [24]

- MMC-based 3PH-DAB

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- Energy balancing
- Q2L mode \& capacitors sizing
- Engagement within bipolar grids

- MMC-based 3PH-DAB


## MMC ENERGY BALANCING AND QUASI SQUARE WAVE OPERATION (I)



MMC operating as a two level converter and its relevant waveforms

## MMC ENERGY BALANCING AND QUASI SQUARE WAVE OPERATION (I)



Ideally, $Q^{+}=Q^{-} \Rightarrow$ Natural balancing

However, reality is different.

- Branch resistances affect the MMC current
- Not all the switches are gated at the same time


Balancing algorithm must be employed!

## MMC ENERGY BALANCING AND QUASI SQUARE WAVE OPERATION (II)



- MMC operating with quasi square voltages and its relevant waveforms


## Quasi Square Wave operation

- Intentional displacement among gating signals
- Control of MFT voltage slopes (dV/dt)
- Control of SMs' voltages!

$$
G=\frac{V_{0} m_{T}}{V_{i n}}
$$

For $\mathrm{G}=1, \mathrm{SMs}$ charge distribution can be derived.


- Charge received by a SM depending upon the gate signal [25]


## MMC ENERGY BALANCING AND QUASI SQUARE WAVE OPERATION (II)



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G=\frac{V_{0} m_{T}}{V_{i n}}
$$

For $\mathrm{G}=1, \mathrm{SMs}$ charge distribution can be derived.


- Charge received by a SM depending upon the gate signal [25]
$\Rightarrow$ Different charge distribution enables balancing!


## QUASI TWO-LEVEL (Q2L) CONVERTER

- MMC-alike structure
- Branch inductors removed!
- SM = Main Switch + Active Snubber
- Sequential insertion/bypassing of SMs [26]

- Example of the Q2L Converter transition $(\mathrm{N}=3)$
- Quasi Two-Level Converter
[26] Stefan Milovanovic and Drazen Dujic. "Comprehensive analysis and design of a quasi two-level converter leg." CPSS Transactions on Power Electronics and Applications 4.3 (2019), pp. 181-196


## QUASI TWO-LEVEL (Q2L) CONVERTER

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- Quasi Two-Level Converter

- Example of the Q2L Converter transition ( $\mathrm{N}=3$ )
\& Every dwell interval introduces new resonant parameters to the circuit!
[26] Stefan Milovanovic and Drazen Dujic. "Comprehensive analysis and design of a quasi two-level converter leg." CPSS Transactions on Power Electronics and Applications 4.3 (2019), pp. 181-196
EPFL


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- Example of the Q2L Converter transition ( $\mathrm{N}=3$ )


Output current drifts to a single branch. Common mode current does not exist!
26] Stefan Milovanovic and Drazen Dujic. "Comprehensive analysis and design of a quasi two-level converter leg." CPSS Transactions on Power Electronics and Applications 4.3 (2019), pp. 181-196

## Q2L CONVERTER - PROS AND CONS



- Observed Q2L configuration

- Relevant waveforms of the Q2L converter operating as the 3PH-DAB


## Q2L CONVERTER - PROS AND CONS



- Observed Q2L configuration

SM capacitor = "short-interval" energy buffer


- Relevant waveforms of the Q2L converter operating as the 3PH-DAB

- Observed Q2L configuration

Pros

- Significant reduction in submodule capacitance
- Converter size reduction (no branch inductors, small SM capacitance)
- Active snubber switch can be sized for half the rated current


## Cons

- Need for HV/MV input/output capacitor
- Complicated analysis of transition process/SM capacitance sizing
- Relevant waveforms of the Q2L converter operating as the 3PH-DAB
- SM capacitance sizing influenced by the branch stray inductance


## SCOTT MFT BASED DC-DC

Medium Frequency Conversion, High Power, Redundancy

## BIPOLAR DC SYSTEM

- Provided ratings

| Parameter | Value |
| :--- | :---: |
| Input voltage $\left(V_{i n}\right)$ | $\pm 20 \mathrm{kV}$ |
| Output voltage $\left(V_{0}\right)$ | 1.5 kV |
| Rated power $\left(P_{\text {nom }}\right)$ | 10 MW |
| Operating frequency $(f)$ | 1 kHz |

## - Redundancy

- Converter structure considering given grid nature?
- Topology
- Operating principles and control
- Operating frequency
- Sizing principles considering given ratings
- Constraints
- Behavior under faults

- Generic structure of a converter to be employed within a bipolar grid


## SIX-STEP MMC-BASED HIGH POWER DC-DC CONVERTER

## Features:

- Both stages switching at MFT operating frequency
- DAB operating principles
- Independent operation of the MMCs (ideally)
- Bidirectional topology
- Bipolar DC grids interface
- Redundant under faulty operating conditions
- Medium frequency operation


## Drawbacks?

- Twelve arm inductors (or six coupled inductors)
- Magnetic coupling (circulating currents)

- Six-Step MMC-Based High Power DC-DC Converter [27]


## MMC-BASED BIDIRECTIONAL DC-DC CONVERTER EMPLOYING STC



- Scott Transformer Connection
- 3PH 3W Tx $\Rightarrow 2 \times 1$ PH Tx
- Number of MMC branches reduction $\left(N_{L} \downarrow\right)$
- Ability to operate in a pure rectifier mode
- Medium frequency operation


28] S. Milovanovic and D. Dujic. "MMC-Based High Power DC-DC Converter Employing Scott Transformer." PCIM Europe 2018. June 2018, pp. 1-7

- MMCs independent operation

$$
\begin{aligned}
& V_{T 1}=m_{T 1} \frac{V_{A B}-V_{C A}}{2} \\
& V_{T 2}=m_{T 2} V_{B C}
\end{aligned}
$$

- Suitable HV side voltages $\left(\mathrm{V}_{\mathrm{C} 1}, \mathrm{~V}_{\mathrm{C} 2}\right)$ ?
- DAB behavior (phase modulated converter)

$$
\begin{aligned}
& P_{1}=\frac{V_{0}^{2} m_{T 1}^{2}}{\omega L_{a}} \varphi_{1}\left(\frac{1}{2}-\frac{3\left|\varphi_{1}\right|}{8 \pi}\right) \\
& P_{2}=\frac{V_{0}^{2} m_{T 2}^{2}}{\omega L_{a}} \varphi_{2}\left(\frac{2}{3}-\frac{\left|\varphi_{2}\right|}{2 \pi}\right)
\end{aligned}
$$

$$
\begin{gathered}
\left(m_{T 1}==\frac{2}{\sqrt{3}} m_{T 2}\right) \wedge\left(\varphi_{1}==\varphi_{2}\right) \\
\Rightarrow P_{1}=P_{2}
\end{gathered}
$$

- Bidirectional topology
- Fundamental frequency switching
- Redundant under faults


(2)


© Converter operation in the case of "Plus" DC pole malfunction

SIMULATION RESULTS (I)

Table 1 Simulated system ratings

| Parameter | Value |
| :--- | :---: |
| Input voltage $\left(V_{\text {in }}\right)$ | $\pm 20 \mathrm{kV}$ |
| Output voltage $\left(V_{0}\right)$ | 1.5 kV |
| Rated power $\left(P_{\text {nom }}\right)$ | 10 MW |
| Operating frequency $(f)$ | 1 kHz |

- $i_{\text {in } 1} \rightarrow \mathrm{MMC}_{1}$ input current
- $i_{\text {in } 2} \rightarrow \mathrm{MMC}_{2}$ input current
- $i_{\text {in }} \rightarrow$ neutral conductor current
- $i_{T 1} \rightarrow \mathrm{~T}_{1}$ P-winding current
- $i_{\text {T2 }} \rightarrow \mathrm{T}_{2}$ P-winding current
- $i_{S} \rightarrow$ LV stage 3PH-currents
- $i_{R} \rightarrow$ SSC output current
- $V_{0} \rightarrow$ load voltage
- $i_{0} \rightarrow$ load current
- $i_{\text {rev }} \rightarrow$ LV side current injection
- $V_{T 1} \rightarrow \mathrm{~T}_{1}$ P-winding voltage
- $V_{T 2} \rightarrow T_{2}$ P-winding voltage

- Converter operating waveforms


## SIMULATION RESULTS (II)

- $i_{\text {in } 1} \rightarrow \mathrm{MMC}_{1}$ input current
- $i_{\text {in2 }} \rightarrow \mathrm{MMC}_{2}$ input current
- $i_{\text {in }} \rightarrow$ neutral conductor current
- $i_{T 1} \rightarrow T_{1}$ P-winding current
- $i_{\text {T2 }} \rightarrow \mathrm{T}_{2}$ P-winding current
- $i_{S} \rightarrow$ LV stage 3 PH -currents
- $i_{R} \rightarrow$ SSC output current
- $V_{0} \rightarrow$ load voltage
- $i_{0} \rightarrow$ load current
- $i_{\text {rev }} \rightarrow$ LV side current injection
- $V_{T 1} \rightarrow \mathrm{~T}_{1}$ P-winding voltage
- $V_{T 2} \rightarrow T_{2} P$-winding voltage

- Converter operating waveforms during five fundamental cycles

MMC-BASED HIGH POWER UNIDIRECTIONAL DC-DC CONVERTER

- No magnetic coupling between Tx windings
- Parameters mismatch robustness
- Sinusoidal operation mode!

- MMC-based High-Power Unidirectional DC-DC Converter

- Converter idealized operating waveforms


## SIMULATION RESULTS (I)

Table 2 Simulated system ratings

| Parameter | Value |
| :--- | :---: |
| Input voltage $\left(V_{\text {in }}\right)$ | $\pm 20 \mathrm{kV}$ |
| Output voltage $\left(V_{0}\right)$ | 1.5 kV |
| Rated power $\left(P_{\text {nom }}\right)$ | 10 MW |
| Operating frequency $(f)$ | 250 Hz |

- $i_{T} \rightarrow$ LV-stage 3PH - currents
- $i_{\text {in } 1} \rightarrow \mathrm{MMC}_{1}$ input current
- $i_{\text {in2 }} \rightarrow \mathrm{MMC}_{2}$ input current
- $V_{1} \rightarrow \mathrm{MMC}_{1}$ AC voltage
- $V_{2} \rightarrow \mathrm{MMC}_{2} \mathrm{AC}$ voltage
- $i_{R} \rightarrow$ DR output current
- $i_{0} \rightarrow$ load current
- $V_{0} \rightarrow$ load voltage
- $i_{T 1} \rightarrow T_{1}$ P-winding current
- $i_{\text {T2 }} \rightarrow T_{2}$ P-winding current
- $V_{T 1} \rightarrow T_{1} P$-winding voltage
- $V_{T 2} \rightarrow T_{2} P$-winding voltage
- $V_{R} \rightarrow$ DR output voltage

- Converter operating waveforms


## SIMULATION RESULTS (II)

- $i_{T} \rightarrow \mathrm{LV}$-stage 3PH - currents
- $i_{\text {in } 1} \rightarrow \mathrm{MMC}_{1}$ input current
- $i_{\text {in2 }} \rightarrow \mathrm{MMC}_{2}$ input current
- $V_{1} \rightarrow \mathrm{MMC}_{1}$ AC voltage
- $V_{2} \rightarrow \mathrm{MMC}_{2} \mathrm{AC}$ voltage
- $i_{R} \rightarrow$ DR output current
- $i_{0} \rightarrow$ load current
- $V_{0} \rightarrow$ load voltage
- $i_{T 1} \rightarrow \mathrm{~T}_{1} \mathrm{P}$-winding current
- $i_{T 2} \rightarrow T_{2}$ P-winding current
- $V_{T 1} \rightarrow \mathrm{~T}_{1}$ P-winding voltage
- $V_{T 2} \rightarrow T_{2} P$-winding voltage
- $V_{R} \rightarrow$ DR output voltage

- Converter operating waveforms during five fundamental cycles

- Series connection of switches
- Series connection of switches with snubbers
- Two-Level voltage waveforms

$\Delta$ Modular Multilevel Converter (MMC)
- Series connection of Submodules (SM)
- Arbitrary voltage waveform generation

- Series connection of MMC-alike SMs
- Quasi Two-Level (trapezoidal) voltage waveform

- Series connection of switches
- Series connection of switches with snubbers
- Two-Level voltage waveforms

- Series connection of Submodules (SM)
- Arbitrary voltage waveform generation

- Series connection of MMC-alike SMs
- Quasi Two-Level (trapezoidal) voltage waveform
$\Rightarrow$ Despite the lack of high voltage semiconductors, we can manage medium/high voltage designs!


## RESONANT CONVERSION

DC-DC Converters, Control Principles, Scalability for High Power Applications

## DC-DC CONVERSION CONCEPTS (I)

## Voltage adaptation in AC and DC systems


(a)

| DC | DC-AC <br> system 1 | MFT <br> converter | AC-DC <br> (arbitrary frequency) <br> converter | DC <br> system 2 |
| :---: | :---: | :---: | :---: | :---: |


(b)

- Principles of interconnecting two networks in case galvanic isolation along with voltage adaptation is needed: (a) Two AC systems; (b) Two DC systems.

- Two AC voltage sources coupled by means of an inductor

$$
\begin{gathered}
v_{1}=\hat{v}_{1} \cos (\omega t) \\
v_{2}=\hat{v}_{2} \cos (\omega t-\delta)
\end{gathered}
$$

$\downarrow$

$$
P_{12}=\frac{\hat{V}_{1} \hat{v}_{2}}{2 \omega L_{y}} \sin (\delta)
$$

## DC-DC CONVERSION CONCEPTS (II)

## Voltage adaptation in AC and DC systems


(a)

| DC | DC-AC <br> system 1 <br> converter | MFT <br> (arbitrary frequency) | AC-DC <br> converter | DC <br> system 2 |
| :---: | :---: | :---: | :---: | :---: |


(b)

- Principles of interconnecting two networks in case galvanic isolation along with voltage adaptation is needed: (a) Two AC systems; (b) Two DC systems.


## Dual-Active Bridge



- Single-Phase Dual-Active-Bridge DAB.


## Resonant Converter



- Series resonant converter.


## SINGLE-PHASE DAB

## Dual-Active Bridge



- 1PH DAB


## Power Transfer

$$
P=\frac{1}{2 \pi} \int_{0}^{2 \pi} V_{p} i_{p}=\frac{V_{1}^{2}}{\omega_{s} L_{\gamma}} \theta\left(1-\frac{\theta}{\pi}\right)
$$

## Presence of high order harmonics

$$
\frac{P}{S_{\mathrm{MFT}}}=\frac{\frac{1}{2 \pi} \int_{0}^{2 \pi} V_{\mathrm{p}} i_{\mathrm{p}}}{V_{\mathrm{p}, \mathrm{RMS}} \mathrm{p}_{\mathrm{RMS}}}=\frac{1-\frac{\theta}{\pi}}{\sqrt{1-\frac{\theta}{2 \pi}}}
$$



- Typical operating waveforms.


## RESONANT CONVERSION

## General structure



- General structure of the resonant converters

$$
\hat{V}_{s w}^{(n)}= \begin{cases}\frac{4 V_{\text {in }}}{\pi n}, & n \text { is odd } \\ 0, & 0 \text { is even }\end{cases}
$$

## Resonant converters

- Series resonant
- Parallel resonant

- Series-Parallel resonant (LCC)
- Series-Parallel resonant (LLC)


## Modeling

- First Harmonic Approximation - FHA
- Piece-wise sinusoidal analysis
- ...
- Spectral content of voltage $v_{s w}$ applied to the resonant tank


## FIRST HARMONIC APPROXIMATION - FHA (I)

## Switching network


(a)

辟

(c)

- (a) FB switching network; (b) FHA principle applied to the FB network; (c) Voltage and current waveforms typical for the switching network.


## Rectifier and filter

v (a) DR with a capacitive filter; (b) DR with an LC filter.


$$
R_{\sigma}=\frac{8}{\pi^{2}} R_{\mathrm{o}}
$$








$$
R_{\sigma}=\frac{\pi^{2}}{8} R_{\mathrm{o}}
$$

## FIRST HARMONIC APPROXIMATION - FHA (II)

## Averaged Model



- Averaged representation of an arbitrary resonant converter in case rectification stage utilizes purely capacitive filter

- Averaged representation of an arbitrary resonant converter in case rectification stage utilizes an LC filter.


## Resonant Tank characteristics



- (left) DR with a capacitive filter; (right) DR with an LC filter.


## RESONANT CONVERTERS (I)

## Series Resonant Converter



- Series resonant converter
- Typical waveforms of an SRC operating at various switching frequencies.



## RESONANT CONVERTERS (II)

## Series Resonant Converter


(a)

(b)

- SRC: (a) Topology; (b) Transfer characteristic derived assuming that $m=1$;


## Parallel Resonant Converter


(a)

$$
\begin{array}{r}
-Q=1-Q=2-Q=3 \\
-Q=4-Q=5
\end{array}
$$


(b)

- SRC: (a) Topology; (b) Transfer characteristic derived assuming that $m=1$;


## SERIES-PARALLEL RESONANT CONVERTER (I)

LCC

(a)

$$
\begin{array}{r}
-Q=1-Q=2-Q=3 \\
V_{\mathrm{o}} / V_{\mathrm{in}} \quad-Q=4-Q=5
\end{array}
$$


(b)

- LCC: (a) Topology; (b) Transfer characteristic derived assuming that $m=1$;
- FHA equivalent of the LCC converter.



## SERIES-PARALLEL RESONANT CONVERTER (II)

LCC


- FHA equivalent of the LCC converter.
- LCC converter transfer characteristics for two different ratios of resonant capacitors and different quality factors. Without loss of generality, MFT turns ratio was set as $m=1$.

(a)

$$
-Q=1-Q=2-Q=3
$$

$$
m V_{\mathrm{o}} / V_{\mathrm{in}} \quad-Q=4-Q=5
$$


(b)

## SERIES-PARALLEL RESONANT CONVERTER (III)

LLC

(a)

$$
-Q=1-Q=2-Q=3
$$


(b)

- LLC: (a) Topology; (b) Transfer characteristic derived assuming that $m=1$;
- Typical waveforms of an LLC operating at various switching frequencies.



## LLC CONVERTER - CONTROL PRINCIPLES (I)

LLC

$\Delta$ FHA equivalent of the LLC converter.
v Transfer characteristics of an LLC converter for different values of quality factor $Q$ and different ratios of resonant inductors $L_{r}$ and $L_{m}$. Without loss of generality, MFT turns ratio was set as $m=1$.


## LLC CONVERTER - CONTROL PRINCIPLES (II)



- One phase-leg of the switching network during the tank voltage transition.
- Resonant tank current during dead-time.



## LLC CONVERTER - CONTROL PRINCIPLES (III)



Converter transfer characteristics zoomed around

- the resonant frequency for two different values of ratio $L m / L r, m=1$.

a Impact of the switching frequency on the voltage gain
- for different quality factors $(Q=[0.05,0.5])[29]$


ム Impact of the quality factor on the voltage gain for different s. switching frequency $\left(f_{s} / f_{0}=[0.95,1.05]\right)$

## LLC CONVERTER - CONTROL PRINCIPLES (III)


[29] Jakub Kucka and Drazen Dujic. "Smooth Power Direction Transition of a Bidirectional LLC Resonant Converter for DC Transformer Applications." IEEE Transactions on Power Electronics 36.6 (2021), pp. $6265-6275$

# COFFEE BREAK 

Well deserved.

## POWER ELECTRONICS SWITCHES: AN ABUNDANCE OF OPTIONS

## Semiconductor devices such as:

- Diodes
- BJTs
- Thyristors
- Triacs
- MOSFETs
- IGBTs
- etc.


## Available in:

- Various voltage/current ratings
- Various packages



## DEVICES FOR MV APPLICATIONS: FEW MAIN CONTENDERS

Two most used options:

- IGBT
- IGCT
- Thyristors and GTOs are clearly still used
Both devices are:
- Fully controllable
- MV rated

Emerging alternatives:

- HV SiC MOSFETs
- HV SiC IGBTs

Both are slowly emerging, but not mature


- 6.5 kV IGBT module and IGCT


## IGBT: CHARACTERISTICS

## IGBTs' main characteristics:

- Insulated gate
- Fully controllable
- Voltage controlled
- High power/voltage ratings
- High switching speed
- Simple integration
- Available as module and press-pack


## Additional benefits:

- Limitation and turn-off of short circuit current
- Low voltage drop in ON state

| Device | Voltage <br> Class [kV] | Current <br> Rating [A] | $V_{\text {ON }}$ <br> @1kA[V] | $V_{\text {ON }}$ <br> @2kA[V] |
| :---: | :---: | :---: | :---: | :---: |
| IGBT/diode | 4.5 | 1600 | 2.30 | 3.40 |
| IGBT/diode | 4.5 | 2000 | 2.55 | 3.65 |
| IGBT | 4.5 | 2100 | 1.90 | 2.70 |
| GTO | 4.5 | 2000 | 2.20 | 2.70 |
| Thyristor | 4.5 | 1150 | 1.35 | 1.65 |
| IGCT/diode | 4.5 | 2200 | 2.00 | 2.50 |
| IGCT | 4.5 | 4000 | 1.50 | 1.80 |

- Typical conduction performance of common semiconductor devices


## Typical ratings for MV IGBTs:

- $4.5 \mathrm{kV}-6.5 \mathrm{kV}$
- $900 \mathrm{~A}-1200 \mathrm{~A}$


## IGBT: PACKAGING AND GATE DRIVE

## Commonly available in:

- Modules
- Press-Pack
- StakPak


## Switching performance:

- Can be externally affected by Gate Drive Unit
- Offers controllable di/dt with adequate gate resistance values

- Does not require external circuitry for safe operation
- IGBT packaging includes modules, press-pack, and StakPak units


## IGCT: CHARACTERISTICS

## IGCTs' main characteristics:

- Thyristor based device
- Lowest conduction loss of fully controllable devices
- Integrated in GDU
- Only available as press-pack
- Snubberless turn-off


## Traditional IGCT application:

- Low frequency (<1 kHz)
- Hard switched


The press-packed GCT is always integrated into the gate driver board to minimise inductance between gate and cathode

## IGCT: COMMON TYPES

## The main types of IGCTs:

- Asymmetric
- Reverse conducting - RC-IGCT
- Reverse blocking - RB-IGCT


## Ratings of the device can be:

- Up to 6.5 kV (engineering samples up to 10 kV )
- Turn-off current higher for asymmetric devices, due to higher thyristor finger surface (up to 6 kA )
- Hard switched


State-of-the-art IGCT device types and their schematic cross sections from top side to bottom side (vertical cross section) [30].


IGCT vs. IGBT. Left: schematic structures of IGCT and IGBT and their plasma distribution during

- conduction. Right: technology curve comparison between 4.5 kV Asymmetric IGCT and StakPak IGBT module at $2.8 \mathrm{kV}, 2 \mathrm{kA}, 125^{\circ} \mathrm{C}$ [30].


## IGCT: LIMITATIONS

## Compared to the IGBT the IGCT:

- Cannot control turn-on di/dt through GDU
- Requires clamp circuitry
- Cannot turn OFF short circuit current
- Has significant GDU power consumption
- Requires bulky GDU capacitors to maintain constant gate-cathode voltage at turn-off

- The IGCT GDU allocated a large portion of its surface to capacitors an turn-off MOSFETs


## IGCT: CLAMP CIRCUIT



- Typical the clamp circuit

- IGCT turn-on not fully controlled by GCU action
- Hard IGCT turn-on forces reverse recovery of complementary device antiparallel diode
- Clamp inductor required to limit antiparallel diode reverse recovery di/dt
- RCD snubber limits the overvoltage
- Part of the energy is recovered back to main DC link


## IGCT IN RESONANT LLC CONVERTER: HIGH FREQUENCY OPERATION

## IGCT frequency limited by:

- Losses and junction temperature
- Gate driver ON/OFF channel capability


## Resonant operation implies:

- Lossless turn-on (ZVS or ZCS)
- Low turn-off loss (low turn-off current)
- Limited di/dt


- Half-bridge based LLC topology and corresponding current waveforms [31]


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- Half-bridge based LLC topology and corresponding current waveforms [31]

LLC topology can greatly exploit IGCT for high-power designs! High frequency operation must be explored!
[31] Dragan Stamenkovic et al. "Soft Switching Behavior of IGCT for Resonant Conversion." 2019 IEEE Applied Power Electronics Conference and Exposition (APEC). 2019, pp. 2714-2719

## IGCT IN LLC: CLAMPLESS OPERATION

## Hard switched IGCT operation required clamp circuit:

- IGCT turn-on causes reverse recovery of complementary antiparallel diode
- Rate of increase of reverse recovery current must be limited by external means


## Soft turn-on removes need for clamp:

- IGCT turn-on occurs while antiparallel diode of the same device is conducting
- Turn-on occurs in ZVS condition

- Current naturally reaches zero in the diode


## Removal of clamp circuit is possible for IGCT in LLC topology:

- Significant space saving
- Significant reduction of component count

- Hard-switched and soft-switched operation differ also by necessity of clamp circuitry [32]


## IGCT IN LLC: SERIES CONNECTION IN HARD SWITCHED APPLICATIONS

## IGCTs in series connection:

- Dynamic voltage balancing provided by RC or RCD snubbers
- Static voltage balancing provided by passive balancing resistors


## Series connection in hard switching:

- Turn-off currents in the kA range
- Snubber capacitance values up to $1 \mu \mathrm{~F}$

- Hard-switched and soft-switched operation differ also by necessity of clamp circuitry


## IGCT IN LLC: SERIES CONNECTION IN SOFT SWITCHED APPLICATIONS

## Challenges in soft switched series connection:

- Low turn-off current increases transitions times
- Large dynamic voltage balancing capacitors unsuitable

For successful series connection in soft switching:

- Ultra-low values of snubber capacitance (<100 nF)
- Purely capacitive snubbers [33]

- IGCT soft-switching in series connection can employ purely capacitive dynamic voltage sharing snubbers


## IGCT IN LLC: HIGH FREQUENCY OPERATION IN SERIES CONNECTION




- During high-frequency series connected operation the duration of switching transitions is not negligible with respect to the switching period [33]

The duration of switching transitions is significant during high frequency series connected operation due to:

- Presence of snubbers increasing the turn-off an turn-on duration
- Short duration of switching period

Additional factors influencing the switching transition duration are:

- Junction temperature
- Level of current pre-flooding as a result of load level


## IGCT IN LLC: CURRENT PREFLOODING

## In resonant IGCT operation the level of current pre-flooding must be accounted

 for as:- In increases the duration of the switching transitions
- It may result in loss of ZVS turn-on


## Loss of ZVS due to current pre-flooding can be counteracted by:

- Increase of turn-off current level
- Reduction of snubber capacitance value (while still maintaining satisfactory dynamic voltage sharing)

- Increase of dead-time duration


Effect of current pre-flooding in series connected IGCTs during turn-off. Top figure

- displays transition at peak conduction current of 100 A , bottom figure peak current of 300 A .


## IGCT IN LLC: THERMAL EFFECTS

Similarly to current pre-flooding level, switching transition duration is also affected by:

- Turn-off current level
- Junction temperature


## Increased turn-off current level results in:

- Faster charge carrier sweep-out at turn-off
- Increased turn-off loss


## Increased junction temperature results in:

- Increased turn-off duration
- Increased turn-off energy



Turn-off duration as a function of turn-off current for series connected IGCTs with snubber capacitance of
A 40 nF (blue), 70 nF (red), and 100 nF (yellow). IGCT switching transition with a $25^{\circ} \mathrm{C}$ difference in junction temperature.

## IGCT IN LLC: IRRADIATION AND TRADE OFFS

Optimisation of the devices on the technology curve is an additional degree of freedom allowing:

- Custom trade-offs between switching and conduction loss
- Reduction of IGCT switching loss in the LLC-SRC topology


## Use of IGCTs in the LLC-SRC topology results in switching loss

 being most significant:- IGCTs are oversized for the tested application
- Extremely low conduction loss as a consequence



Left: conduction loss and; Right: total loss in the tested application at 5 kHz with standard commercial
IGCTs (blue), and devices with respectively $+50 \%$ (red), and $+95 \%$ increased level of electron irradiation
Trade offs:

© Selecting device and tuning operating conditions require some characterization work

# IGCT GATE UNITS FOR SOFT SWITCHING APPLICATIONS 

Design, Soft-switching, and Experience

## REQUIREMENTS (I)

## Gate Commuted Thyristor (GCT)

- Thyristor based technology
- Controlled by current
- Hard driving turn off


## Necessary functions of the gate unit: [34]

- Turn ON
- Turn OFF
- Backporch operation
- Negative-voltage backporch operation
- Retrigger


[^1]
## REQUIREMENTS (II)

## Turn ON

- Similarly to thyristor the turn on requires steep current into the gate
- The value has to be high enough to turn on all gate cells at once
- Gate current peak is approximately 100 to 300 A
- The device opens practically immediately
- The di/dt is limited only by the external circuit

- Simplified illustration of a current pulse applied to the gate

- Reverse conducting IGCT structure


## REQUIREMENTS (III)

## Turn ON

- Similarly to thyristor the turn on requires steep current into the gate
- The value has to be high enough to turn on all gate cells at once
- Gate current peak is approximately 100 to 300 A
- The device opens practically immediately
- The di/dt is limited only by the external circuit


## Hence:

- The gate unit cannot impact GCT turn-on behavior
- The only task of the high turn-on pulse is to avoid hot-spots
- It ensures fast and equal activation of all GCT fingers

- Reverse conducting IGCT structure


## REQUIREMENTS (IV)

## Backporch Operation:

- A certain value of gate current is necessary to keep the IGCT on (if the anode current would drop below the latching current value)
- This current is typically regulated in relation to temperature conditions

$\Delta$ Illustration of backporch current during IGCT conduction


## REQUIREMENTS (V)

## Turn 0FF

- Hard-driving the IGCT by clamping the gate voltage to -20 V [35]
- The initial recombination has to happen within a very short time
$\rightarrow$ high di/dt of gate current is required
$\rightarrow$ low inductance connection of -20 V to gate

- The current plateau equals the anode current
- High power consumption!

4 The IGCT turn OFF event - conducted current is commutated to the gate circuitry

## REQUIREMENTS (VI)

## Turn OFF

- Hard-driving the IGCT by clamping the gate voltage to -20 V [35]
- The initial recombination has to happen within a very short time
$\rightarrow$ high di/dt of gate current is required
$\rightarrow$ low inductance connection of -20 V to gate




## REQUIREMENTS (VII)

## Negative gate voltage Backporch operation

- When the antiparallel diode is conducting, a negative voltage drop over GCT is generated
- The PN junction near anode avalanche breaks and the gate-to cathode voltage becomes negative [36], [37], [38]
- The gate unit typically continues supplying backporch current

- Gate unit during negative gate voltage

$\Delta$ GCT structure


## REQUIREMENTS (VIII)

## Retrigger Pulse

- Once the anode PN junction closes, a gate current pulse is generated to ensure that all thyristor cells are ready to conduct again
- Problem is eventual high di/dt of the load current
- Retrigger current pulse ensures uniform current take over of the GCT fingers

- Retrigger pulse applied to the GCT

- Reverse conducting IGCT structure


## TYPICAL GATE UNIT DESIGNS (I)

## Turn OFF Channel

- The solution for the turn off is practically always the same
- A high number of parallel connected MOSFETs connects a high number of capacitors charged to approx. -20 V to the gate
- High current loading for a very short time
- Parallelization should assure low inductance design

OFF Channel


- Example of the gate OFF circuit implementation


## TYPICAL GATE UNIT DESIGNS (II)

## Turn OFF Channel

- The solution for the turn off is practically always the same
- A high number of parallel connected MOSFETs connects a high number of capacitors charged to approx. -20 V to the gate
- High current loading for a very short time
- Parallelization should assure low inductance design
- Covers a large area on a typical gate unit

- Commercial IGCT - parallel MOSFETs and Capacitors are easily noticable


## TYPICAL GATE UNIT DESIGNS (III)

## Turn On \& Retrigger Channel

- Typically a single channel for both functions
- High-current inductor with low inductance for current build up
- High current MOSFETs with low switching frequency \& a freewheeling diode


ANODE

- Simplified Gate unit turn ON circuitry


## TYPICAL GATE UNIT DESIGNS (IV)

## Backporch Channel

- A typical solution is a buck converter closed-loop controlling the current at high switching frequency
- The required current is only several Amperes


## Negative-Voltage Backporch Channel

- The standard solution is to reduce the backporch current and consume the energy in non-saturated transistors (and resistors) [36], [37]
- Reference [38] provides another solution where the backporch channel utilizes floating power supply


ANODE

- Simplified Gate unit Backporch circuitry


## SOFT-SWITCHING APPLICATION

## Typical IGCT operating conditions

- Switching at high frequency
- Zero-Voltage turn ON
- Low-Current turn Off
- di/dt during switching is limited by resonant tank



## SOFT-SWITCHING APPLICATION

## Typical IGCT operating conditions

- Switching at high frequency
- Zero-Voltage turn ON
- Low-Current turn Off
- di/dt during switching is limited by resonant tank
\& No clamping circuit is necessary!
Atypical loading for IGCT



## GATE UNIT DESIGN (I)

Main Idea

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- Low turn-off current $\rightarrow$ Lower consumption $\rightarrow$ Lower requirements on the turn OFF channel


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- Zero-Voltage Turn ON and limited di/dt during retrigger $\rightarrow$ The magnitude of turn-on gate current pulse can be reduced


## GATE UNIT DESIGN (I)

## Main Idea

- Low turn-off current $\rightarrow$ Lower consumption $\rightarrow$ Lower requirements on the turn OFF channel
- Zero-Voltage Turn ON and limited di/dt during retrigger $\rightarrow$ The magnitude of turn-on gate current pulse can be reducedIntegration of different channels is possible


## GATE UNIT DESIGN (I)

## Main Idea

- Low turn-off current $\rightarrow$ Lower consumption $\rightarrow$ Lower requirements on the turn OFF channel
- Zero-Voltage Turn ON and limited di/dt during retrigger $\rightarrow$ The magnitude of turn-on gate current pulse can be reduced


The size and consumption of the gate unit can be reduced!

## GATE UNIT DESIGN (II)

## SOFTGATE IGCT Gate Unit

- Gate unit tailored for soft switching


## Integration of multiple functions into a single ON channel:

- Turn-ON function
- Retrigger function
- Backporch function
- Negative-Voltage Backporch functions

- Realized SOFTGATE gate unit [39]


## GATE UNIT DESIGN (III)

## OFF Channel

- Optimized for frequent low-current switching
- Utilizing compact polymer tantalum capacitors and low profile MOSFETs
- Tested up to 1.5 kA emergency turn off


- Realized SOFTGATE gate unit


## GATE UNIT DESIGN (IV)

## ON Channel

- T-Type NPC topology with nonlinear inductor
- Capable of controlling the gate current by three voltage levels
- Nonlinear inductor enables fast current build-up for turn on and retrigger current pulses


- Realized SOFTGATE gate unit


## GATE UNIT DESIGN (IV)

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$\Delta$ SOFTGATE ON channel


- Realized SOFTGATE gate unit
- Characteristic of inductor used for the ON channel


## SIZE COMPARISON

The gate unit size can be greatly optimized and reduced for soft-switching applications!


SOFTGATE unit

- Comparison between commercial and SOFTAGE gate unit [40]


## EXPERIMENTAL RESULTS (I)

### 1.44kHz Resonant Operation

- Full load operation
- 2.5 kV dc link
- 140 A turn off current
- 750 A peak current

- Simplifed SOFTGATE circuitry

- SOFTGATE full load operation


## EXPERIMENTAL RESULTS (II)

### 1.44kHz Resonant Operation

- No load operation
- 2.5 kV dc link
- 140 A turn off current

$\Delta$ Simplifed SOFTGATE circuitry


[^2]
## EXPERIMENTAL RESULTS (III)

## Turn Off Detail


$\triangle$ SOFTGATE gate unit


- SOFTGATE turn OFF behaviour


## EXPERIMENTAL RESULTS (IV)

High-Current Emergency Turn Off

- 2 kV
- 1.5 kA
- Estimated gate unit turn off inductance: 1.2 nH

- SOFTGATE gate unit

- SOFTGATE high current turn OFF


## EXPERIMENTAL RESULTS (V)

## 5kHz Resonant Operation

- 2.5 kV dc link
- 16 A turn off current
- 320 A peak current
\& Retrigger function had to be disabled!

$\Delta$ SOFTGATE gate unit


[^3]
## EXPERIMENTAL RESULTS (VI)

## Consumption

- Only 40 W (compared to commercial 58 W)


## Turn OFF details

- Long turn off due to low switching current
- Slow voltage build up


## Thermal run


$\Delta$ Temperatures in steady state


- Turn OFF event


## EXTRA FEATURE

## Shoot-Through Protection

- Since the application does not require clamping circuit a shoot-through might be fatal
- Idea: measure anode-to-cathode voltage to ensure that the diode is conducting before the turn ON [41]

- Protection integrated into SOFTGATE

- Experimental results

[^4]
## CONCLUSIONS

## By tailoring the gate unit for soft-switching:

- The size can be minimized
- The consumption ca be reduced
- 5 kHz resonant operation is feasible with IGCTs..
- ...but a special attention should be paid to details
- IGCT is a preferable switch for a resonant medium-voltage dc transformer



## IGCT RESONANT SWITCHING

Increasing switching frequency through resonant topology

## SRC-LLC TOPOLOGY AND SUBRESONANT OPERATION (I)

## SRC-LLC in subresonant operation

- Often termed as Half-Cycle Discontinuous Mode - HC-DCM

- Half bridge SRC-LLC

- SRC-LLC Subresonant waveforms

- Resonant circuit component

Two resonant frequencies adjusted through design:

- $f_{r}=1 / 2 \pi \sqrt{C_{r} L_{r}}$
- $f_{r 2}=1 / 2 \pi \sqrt{C_{r}\left(L_{r}+L_{m}\right)}$

Switching frequency

- $f_{s}$ - motivated to be high due to MFT


## SRC-LLC TOPOLOGY AND SUBRESONANT OPERATION (II)

SRC-LLC subresonant operation
$m=4.5-Q=0.4-Q=0.6-Q=0.8-Q=1-Q=1.2$


- LLC transfer characteristic

Voltage gain transfer function

$$
\frac{n V_{\text {out }}}{V_{\text {in }}}=\frac{m f_{n}^{2}}{\sqrt{\left(f_{n}^{2}(m+1)-1\right)^{2}+\left(f_{n} m Q\left(f_{n}^{2}-1\right)\right)^{2}}}
$$

Normalized frequency

- $f_{n}=f_{s} / f_{r}$

Inductance ratio

- $m=L_{m} / L_{r}$

Quality factor

- $Q=\frac{\sqrt{L_{\Gamma} / C_{F}}}{n^{2} R_{\text {load }}}$


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Normalized frequency

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Inductance ratio

- $m=L_{m} / L_{r}$

Quality factor

- $Q=\frac{\sqrt{L_{r} / C_{r}}}{n^{2} R_{\text {load }}}$


## No external setpoint

Transfer characteristic ensures power flow

## ZCS: AN INTRODUCTION

## Principles:

- Switching losses proportional to $V \times /$ at time of switching
- Loss reduction achievable through reduction of V or I
- For ZCS, $I=0$ at switching instant
- Forward recovery issues [42]

$\Delta$ Current magnitude at time of turn off is zero.

- Resonant tank resulting in ZCS switching conditions


## ZVS: AN INTRODUCTION

## Principles:

- Similar principle to ZCS, but loss minimisation through $V=0$
- Achieved by conduction of antiparalled diode of device to be turned ON
- Can be affected by load level in SRC-LLC topology

- SRC-LLC Subresonant waveforms displaying ZVS operation


Half bridge SRC-LLC magnetising inductance sustains current in tank until
turn-on

## EXPERIMENTAL IGCT TEST SETUP (II)

## PEL IGCT multifunctional test setup:

- Based on 3L-NPC leg
- Characterization of IGCT during low current turn-off
- Characterization of series connected IGCTs during low current turn-off
- Single pulse tests
- Double pulse tests
- Resonant pulse tests
- Continuous operation with power circulation
- DC link voltage of $2.5 \mathrm{kV}-5 \mathrm{kV}$
- Adjustable resonant frequency

- Flexible and reconfigurable IGCT test setup [43]


## EXPERIMENTAL IGCT TEST SETUP (II)



- (left) ABB ACS1000 water cooled 3L-NPC IGCT stack (DUT); (middle) Custom-built diodes stack; (right) De-ionised water cooling unit

$\Delta$ (left) Custom made amorphous alloy core magnetizing inductor; (middle) Configurable array of eight air core resonant inductors; (right) Reconfigurable resonant capacitor bank


## MINIMISATION OF SWITCHING ENERGY THROUGH ZVS/ZCS (I)

## Problems to address:

- Minimise total switching energy
- Allow increase of switching frequency
- Ensure safe transitions (dead-time)

- Test setup configuration


IGCT turn-off and turn-on under (top) ZVS, (middle) non-ZVS, and (bottom) zero-current conditions. The turn-off current values are $17 \mathrm{~A}, 9 \mathrm{~A}$, and 0 A , respectively. With loss of ZVS partial shoot-though takes place due to incomplete $n$-base sweep-out.

## MINIMISATION OF SWITCHING ENERGY THROUGH ZVS/ZCS (II)



## Variables:

- Dead-time - from $10 \mu$ s to $14 \mu \mathrm{~s}$
- Turn-off current - from 3 A to 15A


## Temperature has visible effect:


^ $T_{j}$ affects and prolongs switching transitions.
© Parametric sweep with different dead-times of o $10 \mu \mathrm{~s}, \mathrm{o} 12 \mu \mathrm{~s}$, and o $14 \mu \mathrm{~s}$, respectively. [44]
[44] Gabriele Ulissi et al. "Resonant IGCT Soft-Switching: Zero-Voltage Switching or Zero-Current Switching?" IEEE Transactions on Power Electronics 37.9 (2022), pp. 10775-10783

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- Turn-off current - from 3 A to 15 A


## Temperature has visible effect:



- $T_{j}$ affects and prolongs switching transitions.


## Minimum loss

It is achieved at limit of ZVS conditions!
© Parametric sweep with different dead-times of o $10 \mu \mathrm{~s}, \mathrm{o} 12 \mu \mathrm{~s}$, and o $14 \mu \mathrm{~s}$, respectively. [44]
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## MINIMISATION OF SWITCHING ENERGY THROUGH ZVS/ZCS (III)

## 3 GCTs devices are tested:

- Standard (5SHX 1445H0001)
- $+55 \%$ irradiated
- +95\% irradiated

Enginering samples are irradiated by HITACHI ENERGY Semiconductors



- GCT forward voltage

- Diode forward voltage


## MINIMISATION OF SWITCHING ENERGY THROUGH ZVS/ZCS (IV)

## Current pre-flooding:

- How much current resonant peak affects turn OFF event?
- Similar studies have been done for IGBT [45], [46]


- Test setup to evaluate pre-flooding effect


## MINIMISATION OF SWITCHING ENERGY THROUGH ZVS/ZCS (V)



- Turn-ON, turn-OFF, and total switching energy for (left) standard commercial RC-IGCTs, (middle) Irradiated A, and (right) Irradiated B devices.
- I off of o $0 \mathrm{~A}, \circ 3 \mathrm{~A}, \circ 6 \mathrm{~A}, \circ 9 \mathrm{~A}, 017 \mathrm{~A}$, and $\circ 34 \mathrm{~A}$
- Dead-time of $14 \mu \mathrm{~s}$


## MINIMISATION OF SWITCHING ENERGY THROUGH ZVS/ZCS (V)



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- Dead-time of $14 \mu \mathrm{~s}$


## HIGH FREQUENCY OPERATION (I)

## Objective:

- Push IGCT to 5 kHz switching frequency
- Ensure safe operating conditions
- Estimate total losses


- GCT forward voltage


A Estimation of losses

- Diode forward voltage


## HIGH FREQUENCY OPERATION (II)



ム De-ionised water cooling unit - limited temperature control.


Few limitations

- Heatsinks could not be preheated
- Limits of industrial cooling unit


## HIGH FREQUENCY OPERATION (III)



## HIGH FREQUENCY OPERATION (IV)



- Measured case temperatures and estimated junction temperatures



ム. Conduction (top) and total loss (bottom) for o standard, o $+55 \%$ irradiated, and $0+95 \%$ irradiated devices

## HIGH FREQUENCY OPERATION (IV)



- Measured case temperatures and estimated junction temperatures


- Conduction (top) and total loss (bottom) for o standard, $0+55 \%$ irradiated, and $0+95 \%$ irradiated devices


## IGCT IN SERIES CONNECTION - HIGH FREQUENCY OPERATION (1)

## Challenges

- Low I off
- Static voltage sharing - not a big problem
- Dynamic voltage sharing
- Snubber capacitance design

- IGCT-based NPC for 6 kV drive [47]



ム Static balancing determined by max leakage current and accepted voltage difference [47]


- Double Pulse test setup arrangement for series connected IGCT tests


## Snubber capacitance values:

- 40 nF
- 70 nF
- 100 nF

Clamp circuit is in use


- Voltage (top) and current (bottom) waveforms during tests


## IGCT IN SERIES CONNECTION - HIGH FREQUENCY OPERATION (III)

$C_{S}=40 \mathrm{nF}$




$$
C_{S}=70 \mathrm{nF}
$$





$$
C_{S}=100 \mathrm{nF}
$$




[^5]
## IGCT IN SERIES CONNECTION - HIGH FREQUENCY OPERATION (IV)

## Operation at 5 kHz demonstrated:

- With standard devices
- With C snubbers only [33]

^ Test setup arrangement for series connected IGCT resonant operation tests
- Typical snubber configurations - Only capacitive snubber is used for resonant switching


## IGCT IN SERIES CONNECTION - HIGH FREQUENCY OPERATION (V)

## Operation at 5 kHz demonstrated:

- With standard devices
- With C snubbers only [33]

- Test setup arrangement for series connected IGCT resonant operation tests


## Ongoing work:

- 10 kV IGCT (engineering samples)
- NPC topology modulation


IGCT voltage (top) and resonant current (bottom) during 5 kHz RC-IGCT series-connected
resonant operation employing a 17 A turn-off current level and only 20 nF snubber capacitance.

- The peak dynamic voltage difference between series connected devices is maintained below the value of 500 V despite the ultra-low capacitance value (dead-time is $20 \mu \mathrm{~s}$ ).


## LUNCH BREAK

Finally..

# DESIGN OF MW MFTS 

What are the design challenges?

## PROBLEM DESCRIPTION

## Multiphysical optimization problem:

## 1) Electrical domain:

- Skin and proximity effects due to the increase of the operating frequency
- Accurate electric parameter design


## 2) Magnetic domain

- Non-sinusoidal excitation
- Core losses (hysteresis and eddy current losses)



## 3) Dielectric domain

- High dV/dt characteristic for the square voltage waveform resulting in over-voltages due to parasitic capacitances
- Insulation coordination


## 4) Thermal domain:

- Thermal coordination
- Increased hot-spot temperatures
- Thermal anisotropy
$\Rightarrow$ MFT design trade-offs: efficiency vs. power density vs. cost vs. manufacturability vs. ...


## SKIN AND PROXIMITY EFFECT

## Effects:

- Non-uniform current density
- Under-utilization of the conductor material
- Localized H-field distortion within the conductor volume
- Impact on conduction losses

- Impact on leakage inductance


## Example of the foil winding MFT geometry cross-section:



- Generic foil winding geometry.
$-0.1[\mathrm{~Hz}](\Delta=0.01)$
* $\Delta$ - the penetration ratio



[^6]
## SKIN AND PROXIMITY EFFECT

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- H and J distribution within the core window area.


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- Generic foil winding geometry.
$0.1[\mathrm{~Hz}](\Delta=0.01)$
$100[\mathrm{~Hz}](\Delta=0.3)$
$1000[\mathrm{~Hz}](\Delta=1)$
$5000[\mathrm{Hz]}(\Delta=2.15)$ $10000[\mathrm{~Hz}](\Delta=3)$
* $\Delta$ - the penetration ratio

^ H and J distribution within the core window area.


## SKIN AND PROXIMITY EFFECT

## Effects:

- Non-uniform current density
- Under-utilization of the conductor material
- Localized H-field distortion within the conductor volume
- Impact on conduction losses
- Impact on leakage inductance


## Example of the foil winding MFT geometry cross-section:



- Generic foil winding geometry.


^ H and J distribution within the core window area.


## INSULATION COORDINATION

MFT geometry cross-section:


HF winding model:


MFT electric parameters:

- Parasitic capacitance cannot be neglected for HF
- Capacitances exist between turns, windings and core
- For pulse excitation voltage distribution is nonlinear
- Higher voltage gradient at the winding input than expected
- Damped oscillatory transient due to turn inductance
- Higher max voltage than expected during transient
- Need for overall insulation reinforcement
- Turn to turn insulation must especially be increased


$$
\begin{gathered}
V(x)=V \frac{\sinh (a x)}{\sinh (a h)} \\
a=\sqrt{\frac{c}{k}}
\end{gathered}
$$

- Insulation coordination problem becomes increasingly difficult with high voltages and frequencies.


## THERMAL COORDINATION (I)

## MFT losses: <br> Qualitative analysis:

- Winding losses
- Core losses


## Heat transfer mechanisms:

- Conduction

- Convection

- Radiation

- Heat transfer

$$
Q_{h}=h A \Delta T
$$

- Temperature gradient

$$
\Delta T=\frac{Q_{h}}{h A}
$$

- Surface decrease $(A \searrow)$ implies temperature increase ( $\Delta T$ )


## Temperature distribution example:



[^7]

## THERMAL COORDINATION (II)

## Core materials:

- Thermal conductivity varies from $4 \mathrm{Wm} / \mathrm{K}$ (ferrites) to $8.35 \mathrm{Wm} / \mathrm{K}$ (nanocrystalline)
- Isotropic thermal conductivity (e.g. ferrites)

- Ferrite core - isotropic.
- Anisotropic thermal conductivity (laminated cores e.g. nanocrystalline)

$\Delta$ Metglas core - anisotropic.


## Windings:

- Copper and Aluminum conductors combined with insulation
- Low $R_{\text {th }}$ along the conductor path due low $R_{\text {th }}$ of Cu and Al
- High $R_{t h}$ in radial direction due to layers of insulation with high $R_{\text {th }}$

$\Delta$ Cross section of a round wire winding [48].


## Winding insulation and cooling:

- Much higher insulation level requirement than within the winding insulation
- Good insulators have very low thermal conductivity (solid or fluid)
- Fluid based insulation provides much better cooling due to convection



## NON-SINUSOIDAL EXCITATION

## Series resonant converter (SRC):



## Characteristic SRC waveforms:



## Core losses:



- AC core losses.


## Winding losses:



- Current harmonics.
- Current waveform impacts the winding losses
- Copper is a linear material
- Losses can be evaluated in harmonic basis
- Current harmonic content must be evaluated
- Total losses are the sum of the individual harmonic losses


## ACCURATE ELECTRIC PARAMETER DESIGN

## Series resonant converter (SRC):



## Characteristic SRC waveforms:



- $V_{1,2}$ square
- I sinusoidal

SRC:

- Leakage inductance is part of the resonant circuit
- It must match the reference:

$$
L_{\sigma . r e f}=\frac{1}{\omega_{0}^{2} C_{r}}
$$

- $\omega_{0}$ is the target resonant frequency
- Magnetizing inductance $L_{m}$ is normally high
- Reduced in the case of LLC converter
- Limits the magnetization current to the reference $I_{m . r e f}$
- Limits the switch-off current and losses:

$$
L_{m}=\frac{n V_{D C 2}}{4 f_{s} I_{\text {m.ref }}}
$$

- Im.ref has to be sufficiently high to maintain ZVS


## MFT DESIGN SPACE

What are the existing technologies and materials?

## DESIGN SPACE EXPLORATION

## Construction choices:

- Transformer types:


Shell type


Core type


C-type


Coaxial type

## Materials:

- Core:
- Silicon steel
- Amorphous
- Nanocrystalline
- Ferrites
- Windings:
- Copper
- Aluminum


## Technologies:

- Insulation:
- Air
- Solid
- Oil
- Cooling
- Air natural/forced
- Oil natural/forced
- Deionized water


## MAGNETIC MATERIALS - SILICON STEEL

## Composition and applications:

- Ferromagnetic material
- Iron based alloy of Silicon provided as isolated laminations
- Mostly used for line frequency transformers


## Advantages:

- Wide initial permeability range
- High saturation flux density
- High Curie-termpature
- Relatively low cost
- Mechanically robust
- Various core shapes available (easy to form)


## Disadvantages:

- High hysteresis loss (irreversible magnetisation)
- High eddy current loss (high electric conductivity)
- Acoustic noise (magnetostriction)

| Saturation B | Init. permeability | Core loss (10 kHz, 0.5T) | Conductivity |
| :---: | :---: | :---: | :---: |
| $0.8 \sim 2.2 \mathrm{~T}$ | $0.6 \sim 100 \cdot 10^{3}$ | $50 \sim 250 \mathrm{~W} / \mathrm{kg}$ | $2 \cdot 10^{7} \sim 5 \cdot 10^{7} \mathrm{~S} / \mathrm{m}$ |



- Example: Measured B-H curve of M330-35 laminate.


## MAGNETIC MATERIALS - AMORPHOUS ALLOY

## Composition and applications:

- Ferromagnetic material
- Iron based alloy of Silicon as thin tape without crystal structure
- For both line frequency and switching frequency applications


## Advantages:

- High saturation flux density
- Low hysteresis loss
- Low eddy current loss (low electric conductivity)
- High Curie-temperature
- Mechanically robust


## Disadvantages:

- Relatively narrow initial permeability range
- Very high acoustic noise (magnetostriction)
- Limited core shapes available (difficult to form)
- Relatively expensive

| Saturation B | Init. permeability | Core loss (10kHz, 0.5T) | Conductivity |
| :---: | :---: | :---: | :---: |
| $0.5 \sim 1.6 \mathrm{~T}$ | $0.8 \cdot 10^{3} \sim 50 \cdot 10^{3}$ | $2 \sim 20 \mathrm{~W} / \mathrm{kg}$ | $<5 \cdot 10^{3} \mathrm{~S} / \mathrm{m}$ |




- Example: Measured B-H curve of Metglas 2605SA.


## MAGNETIC MATERIALS - NANOCRYSTALLINE ALLOY

## Composition and applications:

- Ferromagnetic material
- Iron based alloy of silicon as thin tape with minor portion of crystal structure
- For both line frequency and switching frequency applications


## Advantages:

- Relatively narrow initial permeability range
- High saturation flux density
- Low hysteresis loss
- High Curie-temperature
- Low acoustic noise


## Disadvantages:

- Eddy current loss (compensated thanks to the thin tape)
- Mechanically fragile
- Limited core shapes available (difficult to form)
- Relatively expensive

| Saturation B | Init. permeability | Core loss (10kHz, 0.5T) | Conductivity |
| :---: | :---: | :---: | :---: |
| $1 \sim 1.2 \mathrm{~T}$ | $0.5 \cdot 10^{3} \sim 100 \cdot 10^{3}$ | $<50 \mathrm{~W} / \mathrm{kg}$ | $3 \cdot 10^{3} \sim 5 \cdot 10^{4} \mathrm{~S} / \mathrm{m}$ |




- Example: Measured B-H curve of VITROPERM 500F.


## MAGNETIC MATERIALS - FERRITE

## Composition and applications:

- Ferrimagnetic material
- Ceramic material made from powder of different oxides and carbons
- For both line frequency and switching frequency applications


## Advantages:

- Relatively narrow initial permeability range
- Low hysteresis loss
- Very low eddy current loss
- Low acoustic noise
- Relatively low cost
- Various core shapes available


## Disadvantages:

- Low saturation flux density
- Small mechanical size of cores
- Magnetic properties deteriorate with temperature increase
- Mechanically fragile

| Saturation B | Init. permeability | Core loss (10kHz, 0.5T) | Conductivity |
| :---: | :---: | :---: | :---: |
| $0.3 \sim 0.5 \mathrm{~T}$ | $0.1 \cdot 10^{3} \sim 20 \cdot 10^{3}$ | $5 \sim 100 \mathrm{~W} / \mathrm{kg}$ | $<1 \cdot 10^{-5} \mathrm{~S} / \mathrm{m}$ |



- Example: Measured B-H curve of Ferrite N87.


## WINDING MATERIALS

## Copper winding:

- Flat wire - low frequency, easy to use
- Litz wire - high frequency, limited bending
- Foil - provide flat windings
- Hollow tubes - provide cooling efficiency
- Better conductor
- More expensive
- Better mechanical properties


## Copper parameters:

| Electrical conductivity | $58.5 \cdot 10^{6} \mathrm{~S} / \mathrm{m}$ |
| :---: | :---: |
| Electrical resistivity | $1.7 \cdot 10^{-8} \Omega \mathrm{~m}$ |
| Thermal conductivity | $401 \mathrm{~W} / \mathrm{mK}$ |
| TEC (from $0^{\circ}$ to $\left.100^{\circ} \mathrm{C}\right)$ | $17 \cdot 10^{-6} \mathrm{~K}^{-1}$ |
| Density | $8.9 \mathrm{~g} / \mathrm{cm}^{3}$ |
| Melting point | $1083^{\circ} \mathrm{C}$ |

## Aluminium winding:

- Flat wire
- Foil - skin effect differences compared to Copper
- Hollow tubes
- Difficult to interface with copper
- Offer some weight savings
- Cheaper
- Somewhat difficult mechanical manipulations


## Aluminum parameters:

| Electrical conductivity | $36.9 \cdot 10^{6} \mathrm{~S} / \mathrm{m}$ |
| :---: | :---: |
| Electrical resistivity | $2.7 \cdot 10^{-8} \Omega \mathrm{~m}$ |
| Thermal conductivity | $237 \mathrm{~W} / \mathrm{mK}$ |
| TEC (from $0^{\circ}$ to $\left.100^{\circ} \mathrm{C}\right)$ | $23.5 \cdot 10^{-6} \mathrm{~K}^{-1}$ |
| Density | $2.7 \mathrm{~g} / \mathrm{cm}^{3}$ |
| Melting point | $660^{\circ} \mathrm{C}$ |

## INSULATION

## Multiple influencing factors:

- Operating voltage levels
- Over-voltage category
- Environment - IP class
- Temperature
- Moisture
- Cooling implications
- Ageing (self-healing?)
- Manufacturing complexity
- Partial Discharge, BIL
- Cost


## Dielectric properties:

- Breakdown voltage (dielectric strength)
- Permittivity
- Conductivity
- Loss angle

| Dielectric material | Dielectric strength $\mathbf{( k V} / \mathbf{m m})$ | Dielectric constant |
| :---: | :---: | :---: |
| Air | 3 | 1 |
| Oil | $5-20$ | $2-5$ |
| Mica tape | $60-230$ | $5-9$ |
| NOMEX 410 | $18-27$ | $1.6-3.7$ |
| PTFE | $60-170$ | 2.1 |
| Mylar | $80-600$ | 3.1 |
| Paper | 16 | 3.85 |
| PE | $35-50$ | 2.3 |
| XLPE | $35-50$ | 2.3 |
| KAPTON | $118-236$ | 3.9 |



- Variety of choices available.


## COOLING

## Heat dissipation through heat transfer mechanisms on core and winding surfaces

## Three main cooling methods/media for effective dissipation:

Air:

- Natural convection - inefficient for high power designs
- Forced convection - requires a fan
- Increased complexity, reduced reliability
- For both core and windings
- $2 \mathrm{Amm}^{-2}$ current density


Oil:

- Various mineral oils exist - very efficient
- Forced convection, heat exchangers necessary
- Increased cost, complexity
- High power distribution transformers
- For both core and windings
- $4 \mathrm{Amm}^{-2}$ current density



## Water:

- Forced convection - very efficient
- Hollow conductors for winding cooling
- Ducts/panels for core cooling
- Traction applications
- Indirect water cooling
- 6-7 $\mathrm{Amm}^{-2}$ current density



## Every cooling method requires modeling, trade-off between accuracy and computational cost

## MFT DESIGN DIVERSITY



ABB: $350 \mathrm{~kW}, 10 \mathrm{kHz}$


IKERLAN: $400 \mathrm{~kW}, 1 \mathrm{kHz}$


STS: $450 \mathrm{~kW}, 8 \mathrm{kHz}$


ABB: $3 \times 150 \mathrm{~kW}, 1.8 \mathrm{kHz}$


FAU-EN: 450kW, 5.6 kHz


KTH: $170 \mathrm{~kW}, 4 \mathrm{kHz}$


BOMBARDIER: 350 kW , 8 kHz


EPFL: 300kW, 2kHz


EPFL: $100 \mathrm{~kW}, 10 \mathrm{kHz}$


CHALMERS: $50 \mathrm{~kW}, 5 \mathrm{kHz}$


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$


SCHAFFNER: 5000 kW , 1kHz


IKERLAN: 400kW, 5kHz


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$
$?$

## MFT DESIGN DIVERSITY



ABB: $350 \mathrm{~kW}, 10 \mathrm{kHz}$


IKERLAN: $400 \mathrm{~kW}, 1 \mathrm{kHz}$


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ABB: $3 \times 150 \mathrm{~kW}, 1.8 \mathrm{kHz}$


FAU-EN: 450kW, 5.6 kHz


KTH: $170 \mathrm{~kW}, 4 \mathrm{kHz}$


BOMBARDIER: $350 \mathrm{~kW}, 8 \mathrm{kHz}$


EPFL: 300kW, 2kHz


EPFL: 100kW, 10kHz


CHALMERS: $50 \mathrm{~kW}, 5 \mathrm{kHz}$


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$


SCHAFFNER: $5000 \mathrm{~kW}, 1 \mathrm{kHz}$


IKERLAN: 400kW, 5kHz


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$

Large number of MFT designs has been reported, relying on various combinations of technologies!

## MFT MODELING

What are the necessary models for fast and accurate MFT design?

## MODELING: CORE LOSSES

## Different core loss models:

- Based on characterization of magnetic hysteresis [49], [50], [51]
- Based on loss separation [52]
- Time domain core loss model [53]
- Based on Steinmetz Equation (MSE [54], IGSE [55], iIGSE [56])


## Original Steinmetz Equation:

$$
P_{c}=K f^{a} B_{m}^{\beta}
$$

K, $a, \beta$ - Steinmetz loss coefficients, determined from the core loss dependency graphs $\left(P_{c}\left(B_{m}\right), P_{c}(f)\right)$

## Improved Generalized Steinmetz Equation (IGSE):

$$
\begin{aligned}
& P_{c}=\frac{1}{T} \int_{0}^{T} k_{i}\left|\frac{\mathrm{~d} B(t)}{\mathrm{d} t}\right|^{a}(\Delta B)^{\beta-a} \mathrm{~d} t \\
& k_{i}=\frac{K}{(2 \pi)^{a-1} \int_{0}^{2 \pi}|\cos (\theta)|^{a} 2^{\beta-a} \mathrm{~d} \theta}
\end{aligned}
$$

## Characteristic waveform:



$$
\left|\frac{\mathrm{dB}(t)}{\mathrm{d} t}\right|=\left\{\begin{array}{cl}
0 & \text { for }(1-D) T \\
\frac{2 \Delta B}{D T} & \text { for } D T
\end{array}\right.
$$

## Application of IGSE on the Characteristic Waveform:

$$
\begin{gathered}
P_{s}=2^{a+\beta} k_{i} f^{a} B_{m}^{\beta} D^{1-a} \\
k_{i}=\frac{K}{2^{\beta-1} \pi^{a-1}\left(0.2761+\frac{1.7061}{a+1.354}\right)}
\end{gathered}
$$

## MODELING: WINDING LOSSES

## Foil winding electromagnetic field analysis:

- Dowell's foil winding loss model [57] provides a frequency dependent expression for AC resistance of the windings
- Porosity factor $\eta$ ensures an equal magnetic field for both Litz and foil winding

$$
\eta=d_{e q} \frac{m_{v}}{H_{w}}
$$



$$
\begin{gathered}
P_{\sigma}=\frac{1}{\sigma} \int J J^{*} d v ; \quad P_{\sigma}=\underbrace{\frac{\mathrm{MLT}}{\eta \sigma m_{\mathrm{D}} d_{\text {eq }} H_{w}}}_{R_{\mathrm{DC}}} l_{\mathrm{DC}}^{2}+\left.\sum_{n=1}^{\infty} R_{\mathrm{AC}, n}\right|_{\mathrm{RMS}, n} ^{2} \\
R_{\mathrm{AC}}=F_{\mathrm{r}}(f) \cdot R_{\mathrm{DC}}=\Delta\left[\varsigma_{1}+\frac{2}{3}\left(m_{h}^{2}-1\right) \varsigma_{2}\right] \cdot R_{\mathrm{DC}}, \quad F_{\mathrm{r}}-\text { Resistance factor } \\
\varsigma_{1}=\underbrace{\frac{\sinh (2 \Delta)+\sin (2 \Delta)}{\cosh (2 \Delta)-\cos (2 \Delta)}}_{\text {Skin factor }} ; \quad \zeta_{2}=\underbrace{\frac{\sinh (\Delta)-\sin (\Delta)}{\cosh (\Delta)+\cos (\Delta)}}_{\text {Proximity factor }} ; \Delta=\frac{d_{\mathrm{eq}}}{\delta} \sqrt{\eta} ;
\end{gathered}
$$



$$
\begin{gathered}
d_{e q}=d \sqrt{\frac{\pi}{4}} ; \quad K_{w}=\frac{h_{w}}{d_{w}} ; \\
m_{h}=\sqrt{\frac{N_{S}}{K_{w}}} ; \quad m_{v}=\sqrt{K_{w} N_{s}} ;
\end{gathered}
$$

$h_{w}, d_{w}$ - height and width of a single Litz wire layer; $N_{S}$ - number of strands in a layer;
$m_{v}, m_{h}$ - equivalent number of vertical and horizontal Litz layers in the winding;

## MODELING: LEAKAGE INDUCTANCE

## Application of Dowell's model on the equivalent foil winding:

$$
L_{\sigma}=N_{1}^{2} \mu_{0} \frac{I_{w}}{H_{w}}[\underbrace{\frac{d_{w 1 e q} m_{w 1}}{3} F_{w 1}+\frac{d_{w 2 e q} m_{w 2}}{3} F_{w 2}}_{\begin{array}{c}
\text { Frequency dependent portion due to the magnetic } \\
\text { energy within the copper volume of the windings }
\end{array}}
$$

$+$
Portion due to magnetic energy within the inter-winding dielectric volume
$+\quad d_{w 1 i} \frac{\left(m_{w 1}-1\right)\left(2 m_{w 1}-1\right)}{6 m_{w 1}}$
Portion due to magnetic energy within the inter-layer dielectric of the primary winding

$$
+\underbrace{d_{w 2 i} \frac{\left(m_{w 2}-1\right)\left(2 m_{w 2}-1\right)}{6 m_{w 2}}}
$$

Portion due to magnetic energy within the inter-layer dielectric of the secondary winding
where:

$$
\begin{gathered}
F_{w}=\frac{1}{2 m^{2} \Delta}\left[\left(4 m^{2}-1\right) \varphi_{1}-2\left(m^{2}-1\right) \varphi_{2}\right] \\
\varphi_{1}=\frac{\sinh (2 \Delta)-\sin (2 \Delta)}{\cosh (2 \Delta)-\cos (2 \Delta)} ; \quad \varphi_{2}=\frac{\sinh (\Delta)-\sin (\Delta)}{\cosh (\Delta)-\cos (\Delta)} ;
\end{gathered}
$$

## Winding equivalence:





$$
\Delta^{\prime}=\sqrt{\eta} \Delta ; \quad \eta=d_{e q} \frac{N_{s v}}{H_{w}} ;
$$

$$
m=N_{s h} ;
$$

$d_{i}=\frac{d_{w}-N_{s h} d_{\text {eq }}}{N_{s h}-1} ;$

## Frequency influence:



## MODELING: MAGNETIZING INDUCTANCE

## Magnetic circuit with an air gap:



- Fringing flux must be considered and air gap is often distributed


## Magnetizing inductance calculation:

$$
L_{m}=\frac{\mu_{0} N^{2} A_{c}}{\frac{I_{m}}{\mu_{r}}+d}
$$

Air gap calculation:

$$
d=\mu_{0} \frac{N^{2} A_{c}}{L_{m}}-\frac{I_{m}}{\mu_{r}}
$$

Fringing effect:

$$
L_{m}^{\prime}=L_{m} F_{F R} ; \quad F_{F R}=1+\frac{d}{\sqrt{A_{c}}} \ln \left(\frac{2 H_{w}}{d}\right) ;
$$

Core cross section and window height influence:


## MODELING: HEAT TRANSFER MECHANISMS



MODELING: THERMAL MODEL

## Modes of heat transfer:

- Conduction
- Convection
- Radiation


## Planes of symmetry:



Partitioning into zones:


## Detailed thermal network model:



- Static thermal model can quickly evaluate maximum temperature rise at critical locations

MODELING: THERMAL MODEL

## Modes of heat transfer:

- Conduction
- Convection
- Radiation


## Planes of symmetry:



Partitioning into zones:


Zone1


## Detailed thermal network model:



- Static thermal model can quickly evaluate maximum temperature rise at critical locations

MODELING: THERMAL MODEL

## Modes of heat transfer:

- Conduction
- Convection
- Radiation


## Planes of symmetry:



Partitioning into zones:


Zone1 Top Yoke


## Detailed thermal network model:



- Static thermal model can quickly evaluate maximum temperature rise at critical locations

MODELING: THERMAL MODEL

## Modes of heat transfer:

- Conduction
- Convection
- Radiation


## Planes of symmetry:



Partitioning into zones:


Zone1


## Detailed thermal network model:



- Static thermal model can quickly evaluate maximum temperature rise at critical locations


## MODELING: THERMAL MODEL IMPLEMENTATION

## Implementation of thermal network model:

- Admittance matrix

$$
Q_{(n)}=Y_{t h_{(n \times n)}} \Delta T_{(n)}
$$

- Rearranging the nodes:
- Kron reduction:

$$
\begin{gathered}
\Delta T_{A_{(m)}}=\left(Y_{\text {thAA }_{\left(m_{x} m\right)}}-Y_{\text {thAB }_{\left(m_{x} p\right)}} Y_{t h B B_{\left(p_{x} p\right)}^{-1}}^{-1} Y_{\text {thBA }_{\left(p_{x} m\right)}}\right)^{-1} Q_{A_{(m)}} \\
\Delta T_{A_{(m)}}=Y_{K_{\text {ron }}^{\left(m_{x} m\right)}}^{-1} Q_{A_{(m)}}
\end{gathered}
$$

- Kron matrix:


## Analytical model results for the optimal MFT prototype:

| $T_{1}\left[{ }^{0} \mathrm{C}\right]$ | $T_{2}\left[{ }^{0} \mathrm{C}\right]$ | $T_{3}\left[{ }^{\circ} \mathrm{C}\right]$ | $T_{4}\left[{ }^{0} \mathrm{C}\right]$ | $T_{6}\left[{ }^{0} \mathrm{C}\right]$ | $T_{9}\left[{ }^{0} \mathrm{C}\right]$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 51.3 | 59.9 | 58.4 | 73.75 | 124.6 | 116.3 |

## Detailed thermal network model [61]:



# MFT DESIGN EXAMPLES 

Variety of technological combinations

## TECHNOLOGIES, MATERIALS, DESIGNS

## Construction Choices:

## Materials:

- MFT Types


Shell Type


Core Type


C-Type


Coaxial Type

- Magnetic Materials
- Silicon Steel
- Amorphous
- Nanocrystalline
- Ferrites
- Windings
- Copper
- Aluminum
- Insulation
- Air
- Solid
- Oil
- Cooling
- Air natural/forced
- Oil natural/forced
- Water


ABB: $350 \mathrm{~kW}, 10 \mathrm{kHz}$


IKERLAN: $400 \mathrm{~kW}, 600 \mathrm{~Hz}$


STS: 450kW, 8kHz


ABB: $3 \times 150 \mathrm{~kW}, 1.8 \mathrm{kHz}$


FAU-EN: 450kW, 5.6 kHz


KTH: $170 \mathrm{~kW}, 4 \mathrm{kHz}$


BOMBARDIER: 350 kW , 8 kHz


CHALMERS: 50kW, 5kHz


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$


ALSTOM: 1500kW, 5kHz


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$


EPFL: $100 \mathrm{~kW}, 10 \mathrm{kHz}$


IKERLAN: 400kW, 6kHz


EPFL: 300kW, 2kHz


ACME: ???kW, ???kHz

## ABB MFT - 2002

## Construction

- Shell Type
- Coaxial winding


## Electrical Ratings

- Power: 350kW
- Frequency: 10kHz
- Input Voltage: $\pm 3000 \mathrm{~V}$
- Output Voltage: $\pm 3000 \mathrm{~V}$


## Core Material

- VAC Vitroperm 500F
- U cores


## Windings

- Coaxial (Al inside, Cu outside)


## Cooling

- Winding - De-ionized water
- Core - Air


## Insulation

- Solid

- 350kW MFT by ABB [62]


## MFT dimensions

- Volume: $\approx 37$ I
- V-Density: $\approx 9.5 \mathrm{~kW} / \mathrm{l}$
- Weight: < 50 kg
- W-Density: $\approx 7 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- PD: $38 \mathrm{kV}, 50 \mathrm{~Hz}, 1 \mathrm{~min}$
- BIL: 95 kV (peak), 10 shots

- Multilevel line side converter by ABB (2002)


## ALSTOM MFT - 2003

## Construction

- Single core with multiple windings


## Electrical Ratings

- Power: 1.5MW
- Frequency: 5kHz
- Input Voltage: $\pm 1800 \mathrm{~V}$
- Output Voltage: $\pm 1650 \mathrm{~V}$


## Core Material

- Ferrite
- Size and shape unclear


## Windings

- Litz wire


## Cooling

- Oil (MIDEL)
- Common with power electronics


## Insulation

- Oil (MIDEL)
- Immersed

- 1.5 MW MFT by ALSTOM


## MFT dimensions

- Volume: $0.72 \mathrm{~m}^{3}(2.0 \times 0.73 \times 0.49) \mathrm{m}$
- V-Density: 2.1 kW/I
- Weight: < 1 t (estimation)
-W-Density: < $1.5 \mathrm{~kW} / \mathrm{kg}$ (estimation)


## e-Transformer dimensions

- $(2.1 \times 2.62 \times 0.58) \mathrm{m}$
- Volume: $3.22 \mathrm{~m}^{3}$
- Weight: 3.1 t ( $50 \%$ less)


A e-Transformer by ALSTOM [63], [64]

## ABB MFT - 2007

## Construction

- C-type


## Electrical Ratings

- Power: 75kW (x16)
- Frequency: 400 Hz
- Input Voltage: $\pm 1800 \mathrm{~V}$
- Output Voltage: $\pm 1800 \mathrm{~V}$


## Core Material

- SiFe
- Custom made sheets


## Windings

- Bar wire


## Cooling

- Oil
- Common with power electronics


## Insulation

- Oil
- Immersed

- Enclosure with 16 MFTs by ABB


## MFT dimensions

- Volume: not reported
- V-Density: ? kW/l
- Weight: not reported
- W-Density: ? kW/kg


## PETT dimensions

- Volume: $20 \%$ less
- Weight: $50 \%$ less
- Efficiency: 3\% increase

- PETT by ABB [65]


## BOMBARDIER MFT - 2007

## Construction

- Core Type
- Hollow conductors


## Electrical Ratings

- Power: 350kW (500kW peak)
- Frequency: 8 kHz
- Input Voltage: $\pm 1000 \mathrm{~V}$
- Output Voltage: $\pm 1000 \mathrm{~V}$


## Core Material

- Nanocrystalline
- U cores


## Windings

- Hollow tubes


## Cooling

- Winding - De-ionized water
- Core - Water cooled heatsink


## Insulation

- Solid

- 350kW MFT by Bombardier [66]


## MFT dimensions

- Volume: not reported
- V-Density: ? kW/l
- Weight: 18 kg
- Density: $\approx 7 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- PD: $33 \mathrm{kV}, 50 \mathrm{~Hz}$
- BIL: 100 kV (1.2/50)

- Medium frequency topology by Bombardier


## ABB MFT - 2011

## Construction

- C-core
- Assembly with 3 MFTs


## Electrical Ratings

- Power: 150kW
- Frequency: 1.75 kHz
- Input Voltage: $\pm 1800 \mathrm{~V}$
- Output Voltage: $\pm 750 \mathrm{~V}$


## Core Material

- Nanocrystalline
- C-cut cores


## Windings

- Bar wire



## Cooling

- Oil

Insulation

- Oil
- Immersed

- $3 \times 150 \mathrm{~kW}$ MFT by ABB


## MFT dimensions

- Volume: $\approx 80$ I
- V-Density: $\approx 2.4 \mathrm{~kW} / \mathrm{I}$
- Weight: $\approx 170 \mathrm{~kg}$
- W-Density: $\approx 1.1 \mathrm{~kW} / \mathrm{kg}$


## PETT dimensions

- Weight: 4.5 t

- PETT tank with magnetics by ABB [10], [11]


## UEN MFT - 2011

## Construction

- Core Type


## Electrical Ratings

- Power: 450kW
- Frequency: 5.6 kHz
- Input Voltage: $\pm 3600 \mathrm{~V}$
- Output Voltage: $\pm 3600 \mathrm{~V}$


## Core Material

- Nanocrystalline VITROPERM 500F
- U cores


## Windings

- Aluminum
- Hollow profiles


## Cooling

- Winding - de-ionized water
- Core- Oil


## Insulation

- Oil - Immersed (primary to secondary)
- NOMEX - between turns

- 450kW MFT by UEN [67], [68], [69]


## MFT dimensions

- Volume: not reported
- V-Density: ? kW/I
- Weight: $24-38.2 \mathrm{~kg}$
- W-Density: $\approx 18.8-11.8 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- Designed for 25 kV railway lines
- PD, BIL: not reported

- MFT by UEN


## ETHZ PES MFT - 2014

## Construction

- Shell Type
- for the use with HC-DCM-SRC


## Electrical Ratings

- Power: 166kW
- Frequency: 20kHz
- Input Voltage: $\pm 1000 \mathrm{~V}$
- Output Voltage: $\pm 400 \mathrm{~V}$


## Core Material

- Nanocrystalline Vitroperm 500F
- C-cores


## Windings

- Square Litz Wire


## Cooling

- Water-cooled heat sinks


## Insulation

- Solid
- Mica tape


A 166kW MFT by ETH [70], [71], [72]

## MFT dimensions

- Volume: $\approx 51$
- V-Density: $\approx 32.7 \mathrm{~kW} / \mathrm{I}$
- Weight: $\approx 10 \mathrm{~kg}$
- W-Density: $\approx 16.6 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- No details provided


Nanocrystalline MFT by ETHZ

## ETHZ PES MFT - 2014 (CONT.)

## Construction

- Shell Type
- for the use with TCM-DAB


## Electrical Ratings

- Power: 166kW
- Frequency: 20 kHz
- Input Voltage: $\pm 750 \mathrm{~V}$
- Output Voltage: $\pm 750 \mathrm{~V}$


## Core Material

- Ferrite N87
- U-cores U96/76/30


## Windings

- Square Litz Wire


## Cooling

- Winding - Forced air
- Core - Heatsinks (Forced air)


## Insulation

- PTFE (teflon)

- 166 kW MFT by ETH [70]


## MFT dimensions

- Volume: $\approx 20$ I
- V-Density: $\approx 8.21 \mathrm{~kW} / \mathrm{I}$
- Weight: not reported
- W-Density: not reported


## Insulation Tests

- No details provided

- Ferrite MFT by ETHZ


## STS MFT - 2015

## Construction

- Core Type


## Electrical Ratings

- Power: 450kW
- Frequency: 8kHz
- Input Voltage: $\pm 1800 \mathrm{~V}$
- Output Voltage: $\pm 1800 \mathrm{~V}$


## Core Material

- Nanocrystalline
- C cores


## Windings

- Square Litz Wire


## Cooling

- Winding - Oil
- Core - Air cooled


## Insulation

- Solid combined with Oil
- Core in the air

- 450kW MFT by STS


## MFT dimensions

- Volume: ? I
- V-Density: $\approx$ ? kW/I
- Weight: 50 kg
- W-Density: $\approx 9 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- PD: $37 \mathrm{kV}, 50 \mathrm{~Hz}$ (PD < 5pC)
- BIL: not specified


MF Transformer for Traction

Applications

- MF transformer directly linked to catenary ( $15 \mathrm{kV} @ 162 / 3 \mathrm{~Hz}$ $25 \mathrm{kV} @ 50 \mathrm{~Hz}$
- Cascadable -
e. g. $9 \times 450 \mathrm{~kW}=4 \mathrm{MW}$
- High Voltage P.D. stable insulation system up to 37 kVrms (P. D. $<5 \mathrm{pC}$ )
- Switching frequency: 8 kHz
- Power: 450 kW / 600 kVA (single transformer)
- Weight: 50 kg
- Efficiency: 99,7 \%

Your benefits

- Distributed traction power supply possible
- Reducing system weight by $40 \%$
- Long life time due to P. D. free solid-fluid insulation system
- Low noise
- Environmental insulation and cooling system of transformer

MFT by STS

## ABB MFT - 2017

## Construction

- Core Type


## Electrical Ratings

- Power: 240kW
- Frequency: 10kHz
- Input Voltage: $\pm 600 \mathrm{~V}$
- Output Voltage: $\pm 900 \mathrm{~V}$


## Core Material

- Nanocrystalline
- U cores (custom)


## Windings

- Litz Wire (4 parallel)


## Cooling

- Winding - Air
- Core - Air


## Insulation

- Solid - Cast Resin
- Air

- 240kW MFT by ABB [73]


## MFT dimensions

- Volume: $\approx 67.71$
- V-Density: $\approx 3.6 \mathrm{~kW} / \mathrm{l}$
- Weight: $\approx 42 \mathrm{~kg}$
- W-Density: $\approx 5.7 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- PD: $53 \mathrm{kV}, 50 \mathrm{~Hz}$
- BIL: 150 kV

- MFT by $A B B$


## ABB CERN MFT - 2017

## Construction

- Core Type


## Electrical Ratings

- Power: 100kW
- Frequency: $15 \mathrm{kHz}-22 \mathrm{kHz}$
- Input Voltage: $\pm 540 \mathrm{~V}$
- Output Voltage: $\pm 540 \mathrm{~V} \times 24$


## Core Material

- Nanocrystalline
- U cores


## Windings

- Litz Wire


## Cooling

- Winding/Core - Oil Immersed
- MFT assembly - Air


## Insulation

- Oil (Ester)
- 100kW MFT by ABB [74]


## MFT dimensions

- Volume: $\approx 91$ I ( 61 I without heatsink)
- V-Density: $\approx 1.1 \mathrm{~kW} / \mathrm{l}$
- Weight: $\approx 90 \mathrm{~kg}$
- W-Density: $\approx 1.1 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- PD: $30 \mathrm{kV}, 50 \mathrm{~Hz}$
- BIL: not reported

$\Delta$ MFT by ABB for CERN


## EPFL PEL MFT - 2017

## Construction

- Core Type


## Electrical Ratings

- Power: 100kW
- Frequency: 10 kHz
- Input Voltage: $\pm 750 \mathrm{~V}$
- Output Voltage: $\pm 750 \mathrm{~V}$


## Core Material

- SiFerrite (UU9316 - CF139)
- U cores


## Windings

- Square Litz Wire


## Cooling

- Winding - Air
- Core - Air cooled heatsink Insulation
- Air

- 100kW MFT by EPFL [75], [61], [76]


## MFT dimensions

- Volume: $\approx 12.2 \mathrm{I}$
- V-Density: $\approx 8.2 \mathrm{~kW} / \mathrm{l}$
- Weight: $\approx 28 \mathrm{~kg}$
- W-Density: $\approx 3.6 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- PD: 6kV, 50 Hz
- BIL: not performed

$\Delta$ MFT by EPFL


## ETHZ PES MFT - 2018

## Construction

- Shell Type
- for the use with DC-DC SRC


## Electrical Ratings

- Power: 25kW
- Frequency: 48 kHz
- Input Voltage: $\pm 3.5 \mathrm{kV}$
- Output Voltage: $\pm 400 \mathrm{~V}$


## Core Material

- Ferrite BFM8
- U-cores U96/60/30


## Windings

- Square Litz Wire


## Cooling

- Winding - Forced air
- Core - Forced air


## Insulation

- Dry type - Vacuum poting (windings)

- 25kW MFT by ETH [77]


## MFT dimensions

- Volume: $\approx 3.41$
- V-Density: $\approx 7.4 \mathrm{~kW} / \mathrm{l}$
- Weight: $\approx 6.2 \mathrm{~kg}$
-W-Density: $\approx 4 \mathrm{~kW} / \mathrm{kg}$


## Insulation Tests

- 20kV


Windings/Mold Cover


MV Winding


LV Winding

(b)

## EPFL PEL MFT - 2019

## Construction

- Planar type


## Electrical ratings

- Power: 100kW
- Frequency: 10 kHz
- Input Voltage: $\pm 750 \mathrm{~V}$
- Output Voltage: $\pm 750 \mathrm{~V}$


## Core material

- Nanocrystalline VITROPERM 500F
- U cores


## Cooling

- Winding - Forced air
- Core - Heatsinks (Forced air)


## Insulation

- Solid - Cast resin

- 100kW Planar MFT by PEL.

MFT dimensions

- Volume: 18.51
- V-Density: $5.4 \mathrm{~kW} / \mathrm{I}$
- Weight: 26.3 kg
- W-Density: $3.8 \mathrm{~kW} / \mathrm{kg}$

Insulation tests

- PD: 5kV, 50Hz
- BIL: not reported

- MFT by PEL.


## RWTH SCHAFFNER MFT - 2019

## Construction

- 3-phase Core type


## Electrical ratings

- Power: 5MW
- Frequency: 1kHz
- Input Voltage:
- Output Voltage:


## Core material

- Grain oriented silicon steel
- U cores


## Cooling

- Winding - Air
- Core - Air


## Insulation

- Core in the air
- NOMEX/Mica tape?
- 5MW 3-phase MFT by Schaffner [78].


## MFT dimensions

- Volume: not reported
- V-Density: not reported
- Weight: less than 700kg
- W-Density: > $7.1 \mathrm{~kW} / \mathrm{kg}$


## Insulation tests

- PD, BIL: not reported

-PD, BL: notrepar

- MFT by Schaffner.


## SUPERGRID INSTITUTE MFT - 2019

## Construction

- Core type


## Electrical ratings

- Power: 100kW
- Frequency: 20 kHz
- Input Voltage: $\pm 1.2 \mathrm{kV}$
- Output Voltage: $\pm 1.2 \mathrm{kV}$


## Core material

- Ferrite
- I cores


## Windings

- Copper

- 100kW MFT by Supergrid Institute [79]


## MFT dimensions

- Volume: not reported
- V-Density: not reported
- Weight: not reported
- W-Density: not reported


## Insulation tests

- PD, BIL: not reported

- MFT by Supergrid Institute.


## EPFL PEL HYOSUNG MFT - 2020

## Construction

- Core type


## Electrical ratings

- Power: 300kW
- Frequency: 20kHz
- Input Voltage: $\pm 1.7 \mathrm{kV}$
- Output Voltage: $\pm 4 \mathrm{kV}$


## Core material

- Nanocrystalline
- UU cores


## Windings

- Copper
- Litz wire


## Cooling

- Winding -Forced air
- Core - Forced air


## Insulation



- 300kW Planar MFT by PEL and Hyosung.


## MFT dimensions

- Volume: 621
- V-Density: 4.8kW/I
- Weight: 39.7 kg
- W-Density: $7.55 \mathrm{~kW} / \mathrm{kg}$


## Insulation tests

- PD: not reported
- BIL: not reported
- Winding - Solid, cast resin
- Core - Air

- MFT by PEL and Hyosung


## ETH MFT - 2021

## Construction

- Air core
- Aluminum conductive shielding


## Electrical ratings

- Power: 166kW
- Frequency: 77.4 kHz
- Input Voltage: $\pm 7 \mathrm{kV}$
- Output Voltage: $\pm 7 \mathrm{kV}$


## Windings

- Copper
- Litz wire
- Cylindrical solenoids


## Cooling

- Winding - Forced air


## Insulation

- NOMEX pressboard


DC-DC Converter waveforms / SRC DCX

$\Delta$ MFT by ETH.

## SUMMARY - MFT DESIGNS

## Variety of MFT designs

- Shell Type, Core Type, C-Type
- Copper, Aluminum
- Solid wire, Hollow conductors, Litz wire, Foil
- SiFe, Nannocrystalline, Amorphous, Ferrite


## Integration with Power Electronics

- Insulation coordination
- Cooling
- Electrical parameters
- Choice of core materials
- Form factor constraints
- Optimization at the system level


## Custom designs prevail

## There is no best design...

Limited commercial options. Example: STS $\Rightarrow$

| Source/ Type | $\begin{gathered} p_{\mathrm{n}} \\ \mathrm{kVA} \end{gathered}$ | Freq. kHz | $\underset{\text { kV }}{U_{\text {iso }}}$ | Core mat.* | Cooling method | Tran. Power density ${ }^{\dagger}$ | $\begin{gathered} \text { Eff.}{ }^{\star} \\ \% \end{gathered}$ | Struct./ Wind. ${ }^{+}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| GE:1992[65] Dry | 50 | 50 | N/A | Ferr. | Air | 12(wt) | $99.4{ }^{\text {a,c }}$ | $\begin{aligned} & \hline \text { Coaxial/ } \\ & \text { Cable } \end{aligned}$ |
| GE:2008[66] Dry | 150 | 10 | N/A | Amor. | Air | N/A | N/A | Core/ Ro. Litz |
| UWM:1995[67] Dry | 120 | 20.4 | N/A | Ferr. | Water | 59.5(vol) | $99.6{ }^{\text {a,c }}$ | $\begin{gathered} \hline \text { Coaxial/ } \\ \text { Cable } \\ \hline \end{gathered}$ |
| $\begin{gathered} \hline \text { ABB:2002[43] } \\ \text { Dry } \\ \hline \end{gathered}$ | 350 | 10 | 15 | Nano. | Water | >7( wt$)^{\ddagger}$ | N/A | $\begin{gathered} \hline \text { Coaxial/ } \\ \text { Cable } \end{gathered}$ |
| $\begin{gathered} \text { ABB:2007[47] } \\ \text { Oil } \\ \hline \end{gathered}$ | 75 | 0.4 | 15 | $\mathrm{Si}-\mathrm{Fe}$ | Oil | N/A | >95 ${ }^{\text {b,c }}$ | So. Cu |
| ABB:2011[50, 52] Oil | 150 | 1.75 | 15 | Nano. | Oil | N/A | $\approx 96^{\text {b,c }}$ | Ro. Litz |
| KTH:2009[68] Oil | 170 | 4 | 30 | Amor. | Water Oil | 3.45(wt) | $99^{a, c}$ | Shell/ Ro. Litz Foil |
| $\begin{gathered} \hline \text { TUD:2005[69, 70] } \\ \text { Dry } \\ \hline \end{gathered}$ | 50 | 25 | N/A | Nano. | Water | $\approx 50$ (vol) | >97 ${ }^{\text {b,c }}$ | $\begin{aligned} & \hline \text { Shell/ } \\ & \text { Foil } \end{aligned}$ |
| $\begin{gathered} \text { Bomb:2007[30] } \\ \text { Dry } \end{gathered}$ | 500 | 8 | 15 | Nano. | Water | 27.8(wt) | N/A | $\begin{aligned} & \text { Shell/ } \\ & \text { Hol. Al } \end{aligned}$ |
| FAU:2011[71] Oil | 450 | 5.6 | 25 | Nano. | $\begin{gathered} \hline \text { Water } \\ \text { Oil } \\ \hline \end{gathered}$ | N/A | N/A | $\begin{aligned} & \text { Core/ } \\ & \text { Hol. Al } \end{aligned}$ |
| $\underset{\text { NCSU:2010 }}{\text { Dry }}{ }^{\text {N }}{ }^{\circ}$ | 10 | 3 | 15 | Amor. | Air | N/A | $\begin{gathered} \hline 96.76^{a, c} \\ \hline 97.3^{u, c} \\ \hline 97.16^{a, c} \\ \hline \end{gathered}$ | $\begin{aligned} & \text { Core/ } \\ & \text { Ro. Litz } \end{aligned}$ |
| NCSU:2012[73] Dry | 30 | 20 | 9.5 | Nano. | Air | N/A | $99.5^{\text {a,d }}$ | Coaxial/ Ro. Litz So. Cu |
| EPFL:2010[8] Dry | 25 | 2 | 8 | Amor. | Air | 2.5 (vol) | $99.13^{\text {a,d }}$ | $\begin{aligned} & \text { Shell/ } \\ & \text { Rec. Litz } \end{aligned}$ |
| IK4:2012[74] ${ }^{\circ}$ |  | <1 |  | $\mathrm{Si}-\mathrm{Fe}$ | Air | 3.41(vol) | $99.36^{\text {a,d }}$ | Shell |
| Dry | 400 | >5 | 18 | Nano. | Fan | 14.88(vol) | $99.76^{\text {a,d }}$ | Core |
| ETH:2013[14, 23] ${ }^{\circ}$ | 166 | 20 | N/A | Nano. | Water | 32.7 (vol) |  | Shell/ |
| Dry | 166 |  | N/A | Ferr. | Fan | 8.21 (vol) | $99.4{ }^{4, \tau}$ | Rec. Litz |
| ETH:2015[75] ${ }^{\circ}$ Dry | 25 | 25 | N/A | Ferr. | Air | 8.2 (vol) | N/A | Matrix/ Litz |
|  |  | $\begin{array}{r} 50 \\ \hline 83 \\ \hline \end{array}$ |  |  |  | $\begin{aligned} & 13.3(\mathrm{vol}) \\ & \hline 15.9(\mathrm{vol}) \\ & \hline \end{aligned}$ |  |  |
| Chalm:2016[76] ${ }^{\circ}$ | 50 | 5 | 6 | Nano. | Air | 15.1(vol) | $99.66^{\text {a,c }}$ | $\begin{aligned} & \text { Shell/ } \\ & \text { Rec. Litz } \end{aligned}$ |
| Dry |  |  |  | Ferr. | Air | 11.5(vol) | $99.58{ }^{\text {a,c }}$ |  |
| $\begin{gathered} \text { STS:2014[77] } \\ \text { Oil/Dry }{ }^{\text { }} \\ \hline \end{gathered}$ | 450 | 8 | >30 | N/A | $\begin{aligned} & \hline \text { Oil } \\ & \text { Air } \\ & \hline \end{aligned}$ | 9(wt) | $99.7{ }^{\text {a,c }}$ | $\begin{gathered} \text { Shell// } \\ \text { Litz } \\ \hline \end{gathered}$ |

- Another overview of MFTs reported in literature [81]


# MFT DESIGN OPTIMIZATION 

Optimal design and realization of a 1MW MFT..

## MFT DESIGN METHODS

## Optimization principles:

- Multi-objective problem: non-linear, non-convex, complex
- Optimization objectives: efficiency, weight, volume, cost ...
- Optimization specifications: known parameters, constants
- Optimization variables: continuous and discrete design parameters
- Optimization constraints: any type of limitations
- Optimization time, accuracy, sensibility, robustness


## Genetic algorithm:

- Inheritance, mutation, selection and crossover technique

- Design flowchart using NSGA-II algorithm [82].

1 Global minimum on a frontier

2 Local maximum
3 Inflection point
4 Plateau (local maximum group)

## Neural networks based algorithm:

- Specifications and goals as inputs
- ANN trained with measurements, simulations, datasheets..
- No physics-based models
- Pareto front as output


Training Data (measuscements, simulations, datastects, pappors, tct.)

- 5 - M M M
- Inductor design with the help of ANN [83]


## MFT DESIGN OPTIMIZATION

## Numerous variants of the brute force algorithm for MFT design exist:



EPFL PhD: Villar [84]


EPFL: $300 \mathrm{~kW}, 2 \mathrm{kHz}$


ETHZ PhD: Ortiz [70]


ETHZ: $166 \mathrm{~kW}, 20 \mathrm{kHz}$


EPFL PhD: Mogorovic [85]


EPFL: $100 \mathrm{~kW}, 10 \mathrm{kHz}$

## MFT DESIGN SPECIFICATIONS

## 1 MW DC transformer for MVDC power distribution networks

- Resonant energy conversion, LLC converter
- Bulk power processing
- Reverse conducting IGCTs as switching devices, DI water cooling
- 10 kV (engineering samples) for the primary and 4.5 kV devices for the secondary converter side


## Medium frequency transformer:

- Galvanic isolation, voltage adaptation
- Electrical MFT design requirements:

| Characteristics | Unit | Value |
| :---: | :---: | :---: |
| Frequency | kHz | 5 |
| Nominal Power | MW | 1 |
| Turns Ratio | 1 | $2: 1$ |
| Primary Voltage | kV | $\pm 5$ |
| Secondary Voltage | kV | $\pm 2.5$ |
| Ref. magn. inductance | mH | $25-40$ |
| Ref. leakage inductance | $\mu \mathrm{H}$ | $25-50$ |

- Compromise between multiple design criteria - highest efficiency!

$\Delta$ DC transformer with 3-level NPC power stages, IGCT based.

(a)

(b)
- IGCT stacks used for the two power stages of the 1 MW DCT demonstrator.


## TECHNOLOGIES AND MATERIALS

## Construction Choices:

- MFT Types


Shell Type


Core Type


Coaxial Type

- Winding Types


Litz Wire


Foil


C-Type

## Materials:

- Magnetic Materials
- Silicon Steel
- Amorphous
- Nanocrystalline
- Ferrites
- Windings
- Copper
- Aluminum
- Insulation
- Air
- Solid
- Oil
- Cooling
- Air natural/forced
- Oil natural/forced

Water

## MFT WINDING ARRANGEMENTS

## 1-layer MFT structure:



- Single oil vessel with 1 layer of PW and SW
- PW placed closer to the core limb to reduce its length, due to double number of turns
- Lower pressure drop on PW
- For optimal use of the core window area, different conductor's cross section profiles for PW and SW
- By design selection, PW and SW current densities kept equal
- Simple mechanical realization


## 2-vessel MFT structure:



- Two oil vessels each with 1 layer of PW and SW
- One conductor type for both windings
- Correct turns ratio achieved by external electrical connection, PWs connected in series, SWs in parallel
- Equal current density in both windings
- More complicated realization, requires winding termination panel
- Number of windings doubled compared to 1-layer MFT


## 3-winding MFT structure:



- Single oil vessel with PW interleaved around the SW
- Improved power density with 3 windings
- For optimal use of the core window area, the same conductor type used
- PW current density is 2 times smaller than the SW one
- Necessary turns ratio can be achieved inside or outside the oil vessel


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- Single oil vessel with 1 layer of PW and SW
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## MFT DESIGN ALGORITHM

## Design optimization algorithm flowchart:



## 1) User-defined inputs:

- Electrical requirements
- Insulation, thermal, mechanical constraints (flags)
- Data sheets and material characteristics


## 2) Design optimization variables:

| Var. | Min. | Max. | Res. | Description |
| :---: | :---: | :---: | :---: | :---: |
| $D_{i}$ | 3 mm | 8 mm | 16 | Inner diameter |
| $\delta$ | $0.9 \delta_{C u}$ | $2.2 \delta_{C u}$ | 14 | Wall thickness |
| $N_{S W}$ | 10 | 45 | 36 | SW turns number |
| $K_{b m}$ | 0.2 | 0.9 | 80 | Flux density ratio |

3) Design evaluation based on models, design filters and flags:

- Pipe winding loss model
- Thermal-hydraulic model of the oil
- Core to winding loss ratio ( $R_{w c}$ )
- Minimal current and power density

4) Storing of valid MFT designs

Additional MFT models required!!

## THERMAL-HYDRAULIC MODEL (I)

## Basic approach of modeling: [86]

- Principles of heat and mass conservation
- Pressure equilibrium in closed oil loops


## Thermal part:

- Heat exchange phenomenon
- Four characteristic oil temperatures estimated:

$$
T_{\text {otr }}, T_{\text {otw } 1}, T_{\text {otw } 2}, T_{\text {ob }}
$$

## Energy balance equation for zone $Z_{0}$ :

$$
\begin{aligned}
& z P_{y 1}-P_{\mathrm{w}, 0}-P_{\mathrm{h}, \mathrm{t}}^{A_{0}}-P_{\mathrm{h}, \mathrm{~b}}^{A_{0}}=\rho c_{p} Q_{0}\left(T_{\mathrm{otr}}-T_{\mathrm{ob}}\right) \\
& Q_{0}=A_{0} W_{0}, \quad P_{\mathrm{h}, \mathrm{~b} / \mathrm{t}}^{A_{0}}=A_{0} k_{p}^{h}\left(T_{0 \mathrm{~b} / \mathrm{otr}}-T_{\mathrm{a}, 1}\right)
\end{aligned}
$$

- $z$ - ratio of $P_{\gamma 1}$ that heats the oil in zone $Z_{0}$
- $P_{\gamma 1}$ - excess PW loss that goes to oil
- $P_{w, 0}$ - exchanged heat along the outer vertical wall
- $\rho$ - oil density at $T_{\text {ob }}$
- $C_{p}$ - specific heat capacity at $T_{\text {ob }}$
- $Q_{0}$ - average volumetric oil flow in $Z_{0}$
- $w_{0}$ - average oil velocity in $Z_{0}$
- $A_{0}$ - horizontal cross section area of $Z_{0}$
- $k_{p}^{h}$ - total heat transfer coefficient (HTC)


## Many assumptions:

- Foil winding approximation, steady-state
- Stabilized, laminar oil flow, single phase


## Hydraulic part:

- Two closed oil circulation paths $\left(A B C_{0} D_{0} A\right.$ and $\left.A B C_{i} D_{i} A\right)$


## Pressure equilibrium:

$$
\begin{aligned}
p_{\text {eq,o }} & : p_{T, A B C_{0} D_{0} A}=\Delta p_{1}+\Delta p_{0} \\
p_{\text {eq,i }, i} & : p_{T, A B C_{i} D_{i} A}=\Delta p_{1}+\Delta p_{2}
\end{aligned}
$$

## Produced pressure:

$$
p_{T, A B C_{0} D_{0} A}=\rho g \beta\left(\frac{1}{2} T_{\mathrm{otr}}-T_{\mathrm{a}, 1}+\frac{1}{2} T_{\mathrm{ob}}-\Delta T_{0-\mathrm{a}}\right)
$$

- $\beta$ - oil volume expansion coefficient
- $g$ - gravity


## Pressure drop:

$$
\Delta p_{0,1,2}=\xi \frac{\rho w_{0,1,2}^{2}}{2} \quad \text { with } \quad \xi=\lambda \frac{l}{D_{h}}
$$

- $\xi$ - pressure drop coefficient
- $\lambda$ - friction coefficient
- $D_{h}$ - hydraulic diameter
- 1 - conduit length

- 2 D front view of a single oil vessel

- 2 D top view of a single oil vessel.


## THERMAL-HYDRAULIC MODEL (II)

## Analytical part of THM:

- Four oil temperature expressions - $T_{\text {otr }}(x), T_{\text {ob }}(x), T_{\text {otw1 }}(x), T_{\text {otw2 }}(x)$
- Two pressure balance equations - $p_{\text {eq }, 0}(x), p_{\text {eq }, i}(x)$


## Multi-objective optimization:

| $\underset{x}{\operatorname{minimize}}$ | $f(x), g(x)$ |
| :--- | :--- |
| subject to | $B_{l} \leq x \leq B_{h}$ |

$$
\begin{gathered}
f(x)=\sum_{i=0 \text { tr,otw } 1, \text { otw } 2,0 \mathrm{ob}}\left|T_{i}(x)-T_{i}^{*}\right| \\
g(x)=\left|p_{\text {eq,oo }}(x)+p_{\text {eq, },(x)}\right|
\end{gathered}
$$

- $x$ - set of optimizable parameters $\left\{w_{0}, w_{2}, z, y, k_{p}^{0}, k_{p}^{i}, k_{p}^{h}, a_{1}, a_{2}\right\}$

- 2 D front view of a single oil vessel.
- $T_{i}^{*}$ - experimental thermal measurements
- $a_{1}, a_{2}$ - convective HTCs (oil in $Z_{0}$ and PW; oil in $Z_{2}$ and $S W$ ); $k_{p}^{0}, k_{p}^{j}$ - total HTC (air and oil in $Z_{0}$; air and oil in $Z_{2}$ )


## THM Experimental setup:

- DC source used to induce winding losses: (250 A - 450 A) corresponds to ( $1 \mathrm{~kW}-3 \mathrm{~kW}$ )

- Schematic of the experimental setup.

- Oil vessel instrumented with thermocouples.

- 2D top view of a single oil vessel.


## THERMAL-HYDRAULIC MODEL (III)

## Experimental oil thermal measurements:

- Measured characteristic oil temperatures averaged:

$$
\begin{gathered}
T_{\mathrm{ob}}^{*}=\operatorname{avg}\left(B_{1}, B_{2}, B_{3}, B_{4}, B_{5}, S_{8}\right), T_{\mathrm{otr}}^{*}=\operatorname{avg}\left(T_{1}, S_{1}\right) \\
T_{\text {otw } 1}^{*}=\operatorname{avg}\left(T_{2}, T_{5}\right), T_{\text {otw } 2}^{*}=\operatorname{avg}\left(T_{3}, T_{4}\right)
\end{gathered}
$$

## 18 thermocouples in the same vertical plane placed equidistantly:

- 5 at the top $\left(T_{1}-T_{5}\right)$
- 5 at the bottom $\left(B_{1}-B_{5}\right)$
- 8 on the side $\left(S_{1}-S_{8}\right)$

^ Thermocouples' positions.



- Measurements at 420 A and 23 ml s


## Results [86]:

- Overall good agreement between the THM and measured temperatures
- Highest deviation of $4.2^{\circ} \mathrm{C}$ for $T_{\text {ob }}$ at 310 A operating point
- Improved THM accuracy with higher winding losses, i.e. temperatures
- Experimental measurements versus the THM output for various operating points at $23 \mathrm{~mL} \mathrm{~s}^{-1}$ :



## MODELING: WINDING LOSSES

An extension of the existing Dowell's model based on FEM simulations: [87]

- Hollow penetration ratio $\Delta_{h}$ with hollow permeability $x=\frac{t_{r}}{d_{r, s}}$ :

$$
\Delta_{h}=x \Delta \quad \Rightarrow \quad \Delta_{h}=\frac{t_{r}}{\delta}
$$

- Hollow resistance factor $F_{h}$ - ratio of the AC resistance of the hollow and the solid winding

$$
F_{h}=\frac{R_{A C, h}}{R_{A C, s}}, \quad R_{A C, s}=F_{r S}\left(\Delta^{\prime}\right) \cdot R_{D C, s}, \quad \text { with } \quad \Delta^{\prime}=\sqrt{\eta} \Delta
$$



- $F_{h}$ dependency investigated on 4 parameters: $m, d, f, \Delta_{h}$.
- AC resistance of hollow conductor obtained in simulation of 1080 different models
- From pipes to foils which extend over the full window height.
- Green - square conductor; black - round conductor

- Varied number of layers $m$ in SW.

$\Delta$ Varied external diameters $d$ in $\mathrm{SW}, \mathrm{m}=1$.

$\Delta \Delta_{h}-F_{h}$ curves of SW at different frequencies.
- Optimal $\Delta_{h}$ in range [1.2-1.8] for both square and round conductors


## MFT DESIGN RESULTS

Optimal selection: 2-vessel core-type MFT with nanocrystalline material

(a)

- (a) Efficiency vs. weight power density; (b) Efficiency vs. volume power density.
- Applied design filters:

| $R_{W C}$ | $J$ | $\mathrm{~kW} / \mathrm{kg}$ |
| :---: | :---: | :---: |
| $\leq 0.33$ | $\geq 6 \mathrm{~A} \mathrm{~mm}^{-2}$ | $\geq 2$ |

- Optimal MFT design specifications with the highest efficiency:

| $D_{i}$ | $\delta$ | $N_{P W}$ | $N_{S W}$ | $K_{\text {bm }}$ | $P_{\text {loss }, P W}$ | $P_{\text {loss }, S W}$ | $P_{\text {core }}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 7.6 mm | 1.3 mm | 34 | 17 | 0.475 | 2.87 kW | 2.67 kW | 2.67 kW |
| $R_{W c}$ | $J$ | $\mathrm{~kW} / \mathrm{kg}$ | $\mathrm{kW} / \mathrm{l}$ | $W$ | $L$ | $H$ | $\eta$ |
| 0.32 | $6.1 \mathrm{Amm}^{-2}$ | 2.36 | 3.47 | 494 mm | 851 mm | 685 mm | $99.18 \%$ |

## MFT PROTOTYPE ASSEMBLY (I)

Properties of the fully assembled MFT core: [88]

| $A$ | $B$ | $C$ | $D$ | $M_{C}$ |
| :---: | :---: | :---: | :---: | :---: |
| 140 mm | 256 mm | 318 mm | 232 mm | $\approx 324 \mathrm{~kg}$ |

- 4 sets put together to assemble the core
- Rectangular cross section
- Core supplied by Hitachi Metals [89]

(a)

(b)
- Nanocrystalline material: (a) Set of two C-cut cores

(c)

(d)

- Full-scale prototype of the 2-vessel MFT.

(e)
- (a) Side view of the MFT core; (b) Cross section surface of a single C-core; (c) Top view of the upper core half.

88] Nikolina Djekanovic and Drazen Dujic. "Design Optimization of a MW-level Medium Frequency Transformer." PCIM Europe 2022. 2022, pp. 1-10

## MFT PROTOTYPE ASSEMBLY (II)

## Pipe windings assembly:


(a)

(b)

- (a) Spacer positioning inside the vessel; (b) Comb-alike spacers mounted every $60^{\circ}$ on the SW from the inside.

(c)

(d)

(e)
- (a) Mandrel bending approach; (b) Left vessel with oil, spacers and pair of windings; (c) In between the vessels.


## MFT ELECTRICAL PARAMETER TESTING

## Comparison of measured and modeled electrical parameters:

- Leakage inductance

| $L_{\sigma}(\mu \mathrm{H})$ | An.model | FEM | RLC | Bode 100 |
| :---: | :---: | :---: | :---: | :---: |
| 0 Hz | 43.8 | 44.3 | - | - |
| 5 kHz | - | 34 | 38.2 | 37.9 |

- Magnetizing inductance

| $L_{m}(\mathrm{mH})$ | Ref. value | RLC | Bode 100 |
| :---: | :---: | :---: | :---: |
| 5 kHz | $35.77^{*}$ | 36.66 | 36.74 |

*     - corresponds to 1 mm total air gap

Final MFT prototype dimensions:

| $M_{\text {MFT }}$ | $k W / k g$ | $k W / I$ | $W^{*}$ | $L^{*}$ | $H^{*}$ |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 462 kg | 2.17 | 1.59 | 778 mm | 851 mm | 950 mm |



- 1 MW prototype of the 2 -vessel MFT structure.



## COFFEE BREAK

Last one...

## DC POWER DISTRIBUTION NETWORKS

Modeling, Impact of DCT, Operation Performance Assessment

## DC POWER DISTRIBUTION: TRENDS

## Exemplary DC Power distribution network



- DC power distribution network with multiple nodes and one DCT.


## Trends

- DC PDN with integration with renewable and energy storage systems
- DCT connecting different voltage levels
- Interconnected system


## Challenges

- System planning and operation
- Solutions to tackle more and more interconnected systems
- Communication?


## DC PDN MODELING (I)

## DC Power distribution network



- DC power distribution network with six nodes and one DCT.


## DC Power Flow

- Integrated solution with AC power flow
- DC network as a point-to-point connection


## Solutions:

- Use the advantage of dc systems to solve power flow
- Simple and straightforward solutions


## DC Resonance Response

- Power converters with control loop tend to force the system response
- Dynamics between converters and the transient solution are important


## Solutions:

- Impedance analysis
- Space state model of complete system
- Eigenanalysis and Nodal analysis.
- ...


## DC PDN MODELING (I)

## DC Power distribution network



- DC power distribution network


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## DC Resonance Response

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- Dynamics between converters and the transient solution are important


## Solutions:

- Impedance analysis
- Space state model of complete system
- Eigenanalysis and Nodal analysis.

System gets complicated very quickly

## DC PDN MODELING (II)



- Details inside each power converter box. [93]


## Voltage controlled converter (Source)

- Aims to control voltage of dc bus
- Grid Current control (CC)
- Direct Voltage Control (DVC)


## Current/Power controlled converter (Load)

- Aims to consume or inject power in the dc PDN
- Model of Loads and Sources that do not regulate output voltage
- Grid Current Control (CC)


## DCT (Transformer)

- Link between both dc buses
- Open loop; rely on extra features to operate.
- Power Reversal Algorithm (PRA)
- Soft-Start (SS)
- Idling Mode (IdM)
- Black-Start (BS)
- Over-Load (OL).


## STEADY STATE MODEL (I)

## Example 6 nodes DC PDN



- Steady-state representation of the 6 nodes dc PDN.


## STEADY STATE MODEL (I)

## Example 6 nodes DC PDN



- Steady-state representation of the 6 nodes dc PDN.


ム Steady-state circuit and Kirchhoff's Current Law references.


- Steady-state circuit Nodal Analysis references.


## STEADY STATE MODEL (II)

## Example 6 nodes DC PDN



A Steady-state circuit and Kirchhoff's Current Law references.

$$
\left.\begin{array}{c}
\underbrace{\left[\begin{array}{c}
\left(\frac{1}{r_{l t, 1}}+\frac{1}{r_{d c t}}\right) \\
\frac{-1}{r_{d c t, 1}} \\
r_{d c t, 1}
\end{array}\left(\frac{1}{r_{l t, 1}}+\frac{1}{r_{d c t}}\right)\right.}_{A}
\end{array}\right] \underbrace{\left[\begin{array}{l}
V_{2} \\
V_{5}
\end{array}\right]}_{X}=\underbrace{\left[\begin{array}{l}
\frac{V_{d c, 1}}{r_{l t, 1}}-I_{d c}, 1 \\
\frac{V_{d c, 2}}{r_{l t, 3}}-I_{d c}, 2
\end{array}\right]}_{b}
$$



- Steady-state circuit Nodal Analysis references.

$$
a=\left[\begin{array}{cccccc}
1 & -1 & 0 & 0 & 0 & 0 \\
0 & 1 & -1 & 0 & 0 & 0 \\
0 & 1 & 0 & 0 & -1 & 0 \\
0 & 0 & 0 & 1 & -1 & 0 \\
0 & 0 & 0 & 0 & 1 & -1
\end{array}\right]
$$

$$
\underbrace{\left[\begin{array}{ll}
Y_{\text {nodal }} & B \\
C & D
\end{array}\right]}_{A} \underbrace{\left[\begin{array}{c}
V \\
I
\end{array}\right]}_{x}=\underbrace{\left[\begin{array}{c}
J \\
F
\end{array}\right]}_{b}
$$

Solve $A x=b$

## STEADY STATE MODEL (II)

## Example 6 nodes DC PDN



4 Steady-state circuit and Kirchhoff's Current Law references.

$$
\begin{gathered}
\underbrace{\left[\begin{array}{c}
\left(\frac{1}{r_{l t, 1}}+\frac{1}{r_{d c t}}\right) \\
\frac{-1}{r_{d c t}}
\end{array} \begin{array}{c}
\left(\frac{1}{r_{d c t, 1}}+\frac{1}{r_{t t, 1}}+\frac{1}{r_{d c t}}\right)
\end{array}\right]}_{A} \underbrace{\left[\begin{array}{l}
V_{2} \\
V_{5}
\end{array}\right]}_{X}=\underbrace{\left[\begin{array}{l}
\frac{V_{d c}, 1}{r_{t, 1}}-I_{d c, 1} \\
\frac{V_{d c}, 2}{r_{t t, 3}}-I_{d c, 2}
\end{array}\right]}_{b} \\
\text { Solve } A x=b
\end{gathered}
$$

Not scalable


- Steady-state circuit Nodal Analysis references.

$$
a=\left[\begin{array}{cccccc}
1 & -1 & 0 & 0 & 0 & 0 \\
0 & 1 & -1 & 0 & 0 & 0 \\
0 & 1 & 0 & 0 & -1 & 0 \\
0 & 0 & 0 & 1 & -1 & 0 \\
0 & 0 & 0 & 0 & 1 & -1
\end{array}\right]
$$

$$
\underbrace{\left[\begin{array}{cc}
Y_{\text {nodal }} & B \\
C & D
\end{array}\right]}_{A} \underbrace{\left[\begin{array}{c}
V \\
I
\end{array}\right]}_{x}=\underbrace{\left[\begin{array}{c}
J \\
F
\end{array}\right]}_{b}
$$

Solve $A x=b$

## FREQUENCY RESPONSE OF THE DC PDN (I)



## Power converters

- Sources, Loads, Transformers
- Every element in the DC PDN is a switched mode converter
- Closed-loop controlled converters tends to force an operational point
- There are no centralized control or communication between converters, nor access to internal parameters.


## Transmission line

- Impacts in every point of analysis.
- Have large responsibility in the system dynamics.
- DC cables tend to have high capacitance.


## Faults and others

- Faults and extraordinary events cause disturbances in the DC PDN
- Protection of each element is required with proper coordination.
- Details inside each power converter box.
$\Rightarrow$ All elements contribute to the frequency response of DC PDN!


## FREQUENCY RESPONSE OF THE DC PDN (II)

How to get the system frequency characteristics?




- Examples of different perturbation signals.



## Interconnection of two independent systems



- Commercial low voltage, low power, frequency analysers.

^ Programmable ac sources and grid emulators.


## NODAL IMPEDANCE ASSESSMENT (I)

Calculation of $Z_{1,1}$ - DC impedance of DC PDN from Node 1.


- Simplified 6 nodes DC PDN linear equivalent model.


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Calculation of $Z_{1,1}$ - DC impedance of dc PDN from Node 1.


- Simplified 6 nodes DC PDN linear equivalent model.

$$
\begin{gathered}
Y_{n, 3}=c_{d c, 3}+Y_{l, 1} \\
Y_{n, 6}=c_{d c, 6}+Y_{l, 2} \\
Y_{\text {eq }, \text { sec }}=\left[y_{d c t}^{\prime} / /\left(y_{t l, 3}^{\prime}+c_{d c t, 2^{\prime}}+\left(y_{\mathrm{tl}, 4}^{\prime} / / Y_{n, 6^{\prime}}\right)\right)\right] \\
Y_{\text {eq,pri }}=\left(y_{\mathrm{tl}, 2} / / Y_{\mathrm{n}, 3}\right) \\
Y_{\text {eq }, \mathrm{n}, 1}=y_{\mathrm{tl}, 1} / /\left(Y_{\text {eq }, \text { sec }}+Y_{\text {eq }, \text { pri }}+c_{d c t, 2}\right) \\
Y_{11}=Y_{\mathrm{s}, 1}+c_{d c, 1}+Y_{\text {eq }, \mathrm{n}, 1} \\
Z_{11}=Y_{11}^{-1}
\end{gathered}
$$



4 Step-by-step to find equivalent impedance.

## NODAL IMPEDANCE ASSESSMENT (I)

Calculation of $Z_{1,1}$ - DC impedance of DC PDN from Node 1.


- Simplified 6 nodes DC PDN linear equivalent model.

$$
\begin{gathered}
Y_{\mathrm{n}, 3}=c_{\mathrm{dc}, 3}+Y_{\mathrm{l}, 1} \\
Y_{\mathrm{n}, 6}=c_{\mathrm{dc}, 6}+Y_{\mathrm{l}, 2} \\
Y_{\text {eq }, \text { sec }}=\left[y_{\mathrm{dct}}^{\prime} / /\left(y_{\mathrm{tl}, 3}^{\prime}+c_{\mathrm{dct}, 2^{\prime}}+\left(y_{\mathrm{tl}, 4}^{\prime} / / Y_{\mathrm{n}, 6^{\prime}}\right)\right)\right] \\
Y_{\mathrm{eq}, \text { pri }}=\left(y_{\mathrm{tl}, 2} / / Y_{\mathrm{n}, 3}\right) \\
Y_{\mathrm{eq}, \mathrm{n}, 1}=y_{\mathrm{tl}, 1} / /\left(Y_{\mathrm{eq}, \text { sec }}+Y_{\text {eq }, \text { pri }}+c_{\mathrm{dct}, 2}\right) \\
Y_{11}=Y_{\mathrm{s}, 1}+c_{\mathrm{dc}, 1}+Y_{\mathrm{eq}, \mathrm{n}, 1} \\
Z_{11}=Y_{11}^{-1}
\end{gathered}
$$



## NODAL IMPEDANCE ASSESSMENT (II)

## From mass-spring-damper system to .



$$
\left.\begin{array}{rl}
{\left[\begin{array}{cc}
m_{1} & 0 \\
0 & m_{2}
\end{array}\right]}
\end{array}\right]\left[\begin{array}{l}
\ddot{x_{1}} \\
\ddot{x_{2}}
\end{array}\right]+\left[\begin{array}{cc}
b_{1} & 0 \\
0 & b_{2}
\end{array}\right]\left[\begin{array}{l}
\dot{x_{1}} \\
\dot{x}_{2}
\end{array}\right] .
$$



## NODAL IMPEDANCE ASSESSMENT (II)

## From mass-spring-damper system to .



$$
\left.\begin{array}{rl}
{\left[\begin{array}{cc}
m_{1} & 0 \\
0 & m_{2}
\end{array}\right]}
\end{array}\right]\left[\begin{array}{l}
\ddot{x_{1}} \\
\ddot{x_{2}}
\end{array}\right]+\left[\begin{array}{cc}
b_{1} & 0 \\
0 & b_{2}
\end{array}\right]\left[\begin{array}{l}
\dot{x_{1}} \\
\dot{x_{2}}
\end{array}\right] .
$$



$$
\begin{aligned}
& {\left[\begin{array}{cc}
q_{1} & 0 \\
0 & q_{2}
\end{array}\right]\left[\begin{array}{l}
\ddot{v_{1}} \\
\ddot{v_{2}}
\end{array}\right]+\left[\begin{array}{cc}
c_{1} & 0 \\
0 & c_{2}
\end{array}\right]\left[\begin{array}{l}
\dot{v_{1}} \\
\dot{v_{2}}
\end{array}\right] } \\
&+\left[\begin{array}{cc}
y_{1}+y_{2} & -y_{2} \\
-y_{2} & y_{2}+y_{3}
\end{array}\right]\left[\begin{array}{l}
v_{1} \\
v_{2}
\end{array}\right]=\left[\begin{array}{c}
i_{1} \\
0
\end{array}\right]
\end{aligned}
$$

$$
\begin{gathered}
Q \dot{V}+C \dot{V}+Y V=I, \\
C s V e^{s t}+Y V e^{s t}=J e^{s t}, \\
{[C s+Y] V_{\ell}^{s t}=J \ell^{g t}} \\
V=\underbrace{[C s+Y]^{-1}}_{Z} J \\
V=\underbrace{\left[C s+Y_{\text {nodal }}+Y_{s, l}\right]^{-1}}_{H_{z}} /
\end{gathered}
$$

## MODAL RESONANCE ANALYSIS

Impedance transfer function

$$
H_{z}=\psi \wedge \varnothing
$$

Node's participation factor
\& Includes poles of other voltage controllers


- Example of Node 1 impedance with different controller gains



# DCT IN MVDC POWER DISTRIBUTION NETWORKS 

Operation of the system and impact of DCT in the system.

## DCT IN MVDC POWER DISTRIBUTION NETWORKS (I)

## Power Flow of DC PDN, with different DCT location

- Power flow of dc PDN with different relationship of impedances before and after transformer connection.





## DCT IN MVDC POWER DISTRIBUTION NETWORKS (II)

## Frequency response of DC PDN, with different location of DCT

- Node impedance of DCT connection for different connection point. [94]




(b) LV



## DCT IN MVDC POWER DISTRIBUTION NETWORKS (III)

## Connection of extra power converter with...

## System operation + model and extra element information

- Set minimum requirements for extra converter
- Add extra dampers to the system
- Limit regions of connections
- ...


## Knowledge and control of complete system

- Choose extra converter location
- Change Sources' control loop speed
- Change Impedance characteristic of extra converter
- ...

Interconnected system - "Smart Grid"

- Equipment and dc PDN limits

- DC PDN with an extra power converter to be connected to the system.


## DCT IN MVDC POWER DISTRIBUTION NETWORKS (IV)

## Connection of extra power converter

## Choose extra converter location



Frequency response for Sources' impedance for extra element connected to (left)

- Node 3, and (right) Node 2.


- Voltage regulation of the Sources' Nodes with the extra element connected to (left)
- Node 3, and (right) Node 2.


## DCT IN MVDC POWER DISTRIBUTION NETWORKS (V)

## Connection of extra power converter

## Change Sources' control loop speed



Frequency response for the Sources' impedance with the extra element connected to

- Node 3 and voltage controller of (left) Node 4, and (right) Node 1, 10x slower.



Voltage regulation of the Sources' Nodes with extra element connected to Node 3 - and voltage controller of (left) Node 4, and (right) Node 1, 10x slower.

# OPERATIONAL PERFORMANCE ASSESSMENT 

Nodes, Modes, grid configuration, and impedance assessment.

## OPERATIONAL PERFORMANCE ASSESSMENT (I)

Modal response


- Simple Dc PDN with 6 nodes under consideration.

$\Delta$ Modes of the system and its magnitude.

- Participation Factor of each Node to the Mode.


## OPERATIONAL PERFORMANCE ASSESSMENT (II)

## Modal response



- Simple Dc PDN with 6 nodes under consideration.

- Modes of the system and its magnitude.

- Participation Factor of each Node to the Mode.


## OPERATIONAL PERFORMANCE ASSESSMENT (III)

## Nodes of interest. Nodes' characteristics



Illustrative example of radial/mesh configuration for a dc PDN with renewables integration.


- Aerial view of the illustrative dc PDN for the city of Aigle - Switzerland

- Bode plot of impedance measurements in three different nodes (Source node, Load ^ node, and DCT node).


## DIRECT CURRENT TRANSFORMER FEATURES

Operating principles, features, power reversal methods, and practical examples.

## OPERATIONAL PRINCIPLES (I)

## DC Transformer



DCT with NPC power stages for high power and Full-bridge power stages for the
investigation.

## LLC converter benefits

- Open loop operation
- Stiff voltage gain
- High efficiency


## On Features of DC Transformer

- Power Reversal Methods
- Idling Mode Operation
- Soft-start sequence
- Overload Protection
-.


## OPERATIONAL PRINCIPLES (II)

## DC Transformer




- DCT model and characteristic.

DCT 1


- DCT with Full-bridge power stages for the investigation.

DCT 2


- DCT with Full-bridge power stages for the investigation.


Experimental data -
Theorical

## DCT - FEATURES AND EXPERIENCE (I)

## Soft-start strategy




- Soft-start strategy

$\Delta$ Photo of the two low voltage DCTs of the Laboratory.


## DCT - FEATURES AND EXPERIENCE (II)

## Power Reversal Algorithm (I)



- Experimental results for step change.


- Evaluated Methods.


## DCT - FEATURES AND EXPERIENCE (III)

## Power Reversal Algorithm (II)



Power Reversal Methods

v Experimental results for ramp change and zoom in each stage

(a)
(b)
(c)
(d)

## DCT - FEATURES AND EXPERIENCE (IV)

## Idling Mode




- Experimental results for Idling mode and zoom in each stage



## DCT - FEATURES AND EXPERIENCE (V)

## Current limiting and Overload protection



- Current limiting strategy

- Experimental results for current limiting strategy.


## SUMMARY AND CONCLUSIONS

Why DC?, How DC? and When DC?

## MVDC BULK POWER CONVERSION

## MVDC Power Distribution Networks

- Feasibility
- Technology readiness
- Standards


## Conversion

- Modular
- Bulk
- Performances


## Applications

- Business Case - Owner
- Business Case- OEM
- Business Case - in general

- Modular power processing


- Envisioned future MVDC grids and its links with existing grids


## REFERENCES

[1] Uzair Javaid et al. "MVDC supply technologies for marine electrical distribution systems." CPSS Transactions on Power Electronics and Applications 3.1 (2018), pp. 65-76.
[2] Alessandro Clerici, Luigi Paris, and Per Danfors. "HVDC conversion of HVAC lines to provide substantial power upgrading." IEEE transactions on Power Delivery 6.1 (1991), pp. 324-333.
[3] Michael Häusler, Gernot Schlayer, and Gerd Fitterer. "Converting AC power lines to DC for higher transmission ratings." ABB review (1997), pp. 4-11.
[4] D Marene Larruskain et al. "Conversion of AC distribution lines into DC lines to upgrade transmission capacity." Electric Power Systems Research 81.7 (2011), pp. 1341-1348.
[5] D Marene Larruskain et al. "VSC-HVDC configurations for converting AC distribution lines into DC lines." International Journal of Electrical Power \& Energy Systems 54 (2014), pp. 589-597.
[6] ABB. Tjereborg. http://new.abb.com/systems/hvdc/references/tjaereborg.
[7] Charles Bodel. Paimpol-Bréhat tidal demonstrator project. http://eusew.eu/sites/default/files/programme-additional-docs/EUSEW1606160PresentationtoEUSEWbyEDF.pdf. EDF.
[8] G. Bathurst, G. Hwang, and L. Tejwani. "MVDC - The New Technology for Distribution Networks." 11th IET International Conference on AC and DC Power Transmission. Feb. 2015, pp. 1-5.
[9] SP Energy Networks. Angle dc. https://www. spenergynetworks.co.uk/pages/angle_dc.aspx.
[10] D. Dujic et al. "Power Electronic Traction Transformer-Low Voltage Prototype." IEEE Transactions on Power Electronics 28.12 (Dec. 2013), pp. 5522-5534.
[11] C. Zhao et al. "Power Electronic Traction Transformer-Medium Voltage Prototype." IEEE Transactions on Industrial Electronics 61.7 (July 2014), pp. 3257-3268.
[12] M. K. Das et al. " $10 \mathrm{kV}, 120$ A SiC half H -bridge power MOSFET modules suitable for high frequency, medium voltage applications." 2011 IEEE Energy Conversion Congress and Exposition. Sept. 2011, pp. $2689-2692$.
[13] A. Q. Huang. "Medium-Voltage Solid-State Transformer: Technology for a Smarter and Resilient Grid." IEEE Industrial Electronics Magazine 10.3 (Sept. 2016), pp. 29-42.
[14] D. Wang et al. "A 10-kV/400-V 500-kVA Electronic Power Transformer." IEEE Transactions on Industrial Electronics 63.11 (Nov. 2016), pp. 6653-6663.
[15] Xiaodong Zhao et al. "DC Solid State Transformer Based on Three-Level Power Module for Interconnecting MV and LV DC Distribution Systems." |EEE Transactions on Power Electronics 36.2 (2021), pp. 1563-1577.
[16] S. Inoue and H. Akagi. "A Bidirectional Isolated DC-DC Converter as a Core Circuit of the Next-Generation Medium-Voltage Power Conversion System." IEEE Transactions on Power Electronics 22.2 (Mar. 2007), pp. 535-542.
[17] Johann W Kolar and Gabriel Ortiz. "Solid-state-transformers: key components of future traction and smart grid systems." Proc. of the International Power Electronics Conference (IPEC), Hiroshima, Japan. 2014.
[18] R. W. A. A. De Doncker, D. M. Divan, and M. H. Kheraluwala. "A three-phase soft-switched high-power-density DC/DC converter for high-power applications." IEEE Transactions on Industry Applications 27.1 (Jan. 1991), pp. 63-73.
[19] Stefan P Engel, Nils Soltau, and Rik W De Doncker. "Instantaneous current control for the three-phase dual-active bridge DC-DC converter". Energy Conversion Congress and Exposition (ECCE). IEEE. 2012, pp. 3964-3969.
[20] Stefan P Engel et al. "Improved instantaneous current control for the three-phase dual-active bridge DC-DC converter." ECCE Asia Downunder (ECCE Asia). IEEE. 2013, pp. 855-860.
[21] R. Withanage and N. Shammas. "Series Connection of Insulated Gate Bipolar Transistors (IGBTs)." IEEE Transactions on Power Electronics 27.4 (Apr. 2012), pp. 2204-2212.
[22] IA Gowaid et al. "Analysis and design of a modular multilevel converter with trapezoidal modulation for medium and high voltage DC-DC transformers." IEEE Transactions on Power Electronics 30.10 (2015), pp. $5439-5457$.
[23] IA Gowaid et al. "Quasi two-level operation of modular multilevel converter for use in a high-power DC transformer with DC fault isolation capability". IEEE Transactions on Power Electronics 30.1 (2015), pp. 108-123.
[24] Stephan Kenzelmann et al. "Isolated DC/DC structure based on modular multilevel converter." IEEE Transactions on Power Electronics 30.1 (2015), pp. 89-98.
[25] S. Shao et al. "A Capacitor Voltage Balancing Method for a Modular Multilevel DC Transformer for DC Distribution System." IEEE Transactions on Power Electronics 33.4 (Apr. 2018), pp. 3002-3011.
[26] Stefan Milovanovic and Drazen Dujic. "Comprehensive analysis and design of a quasi two-level converter leg." CPSS Transactions on Power Electronics and Applications 4.3 (2019), pp. 181-196.
[27] Stefan Milovanovic and Drazen Dujic. "Six-Step MMC-Based High-Power DC-DC Converter." The 2018 International Power Electronics Conference-IPEC 2018 ECCE Asia. CONF. 2018.
[28] S. Milovanovic and D. Dujic. "MMC-Based High Power DC-DC Converter Employing Scott Transformer." PCIM Europe 2018. June 2018, pp. 1-7.

## REFERENCES

[29] Jakub Kucka and Drazen Dujic. "Smooth Power Direction Transition of a Bidirectional LLC Resonant Converter for DC Transformer Applications." IEEE Transactions on Power Electronics 36.6 (2021), pp. 6265-6275.
[30] Umamaheswara Vemulapati et al. "Recent advancements in IGCT technologies for high power electronics applications." 2015 17th European Conference on Power Electronics and Applications (EPE'15 ECCE-Europe). 2015, pp. 1-10.
[31] Dragan Stamenkovic et al. "Soft Switching Behavior of IGCT for Resonant Conversion." 2019 IEEE Applied Power Electronics Conference and Exposition (APEC). 2019, pp. 2714-2719.
[32] Dragan Stamenković et al. "IGCT Low-Current Switching-TCAD and Experimental Characterization." IEEE Transactions on Industrial Electronics 67.8 (2020), pp. 6302-6311.
[33] Gabriele Ulissi et al. "High-Frequency Operation of Series-Connected IGCTs for Resonant Converters." IEEE Transactions on Power Electronics 37.5 (2022), pp. 5664-5674.
[34] ABB. "Applying IGCT Gate Units." Application Note 5SYA 2031-05 (2017).
[35] Zhengyu Chen et al. "Stray Impedance Measurement and Improvement of High-Power IGCT Gate Driver Units." IEEE Transactions on Power Electronics 34.7 (2019), pp. 6639-6647.
[36] H. Gruening et al. " 6 kV 5 kA RCGCT with advanced gate drive unit." Proceedings of the 13th International Symposium on Power Semiconductor Devices and ICs. IPSD01. 2001, pp. 133-136.
[37] Luyao Xie, Xinmin Jin, and Yibin Tong. "The design of IGCT Gate-Unit equipped in the three-level NPC converter." 2011 International Conference on Electrical Machines and Systems. 2011, pp. 1-6.
[38] H.E. Gruening and K. Koyanagi. "A modern low loss, high turn-off capability GCT gate drive concept." 2005 European Conference on Power Electronics and Applications. 2005,10 pp.-P. 10.

[40] Jakub Kucka and Drazen Dujic. "IGCT Gate Unit for Zero-Voltage-Switching Resonant DC Transformer Applications." IEEE Transactions on Industrial Electronics 69.12 (2022), pp. 13799-13807.
[41] Jakub Kucka and Drazen Dujic. "Shoot-Through Protection for an IGCT-Based ZVS Resonant DC Transformer." IEEE Transactions on Industrial Electronics (2022), pp. 1-1.
[42] Lars Lindenmüller et al. "Loss reduction in a medium frequency series resonance converter by forced evacuation." 2013 IEEE Energy Conversion Congress and Exposition. 2013 , pp. $2044-2051$.
[43] Dragan Stamenkovic. "IGCT Based Solid State Resonant Conversion." PhD thesis. EPFL, 2020.
[44] Gabriele Ulissi et al. "Resonant IGCT Soft-Switching: Zero-Voltage Switching or Zero-Current Switching?" IEEE Transactions on Power Electronics 37.9 (2022), pp. 10775-10783.
[45] Drazen Dujic et al. "Characterization of 6.5 kV IGBTs for High-Power Medium-Frequency Soft-Switched Applications." IEEE Transactions on Power Electronics 29.2 (2014), pp. $906-919$.
[46] G. Ortiz et al. "Soft-switching techniques for medium-voltage isolated bidirectional DC/DC converters in solid state transformers." IECON 2012-38th Annual Conference on IEEE Industrial Electronics Society. 2012, pp. 5233-5240.
 No.00CH37129). Vol. 3. 2000, 1923-1929 vol.3.
[48] M. Jaritz and J. Biela. "Analytical model for the thermal resistance of windings consisting of solid or litz wire." 2013 15th European Conference on Power Electronics and Applications (EPE). Sept. 2013 , pp. 1-10.
 01/15/2016).
[50] F. Preisach. "Über die magnetische Nachwirkung." de. Zeitschrift für Physik 94.5-6 (May 1935), pp. 277-302. URL: http : //link. springer .com/article/10.1007/BF01349418 (visited on 01/15/2016).
[51] J.H. Chan et al. "Nonlinear transformer model for circuit simulation." IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems 10.4 (Apr. 1991 ), pp. $476-482$.
[52] G. Bertotti. "Some considerations on the physical interpretation of eddy current losses in ferromagnetic materials." Journal of Magnetism and Magnetic Materials 54 (Feb. 1986), pp. 1556-1560. URL: http://www.sciencedirect.com/science/article/pii/0304885386909261 (visited on 01/15/2016).
[53] D. Lin et al. "A dynamic core loss model for soft ferromagnetic and power ferrite materials in transient finite element analysis." IEEE Transactions on Magnetics 40.2 (Mar. 2004), pp. 1318 -1321.
[54] J. Reinert, A. Brockmeyer, and R.W.A.A. De Doncker. "Calculation of losses in ferro- and ferrimagnetic materials based on the modified Steinmetz equation." IEEE Transactions on Industry Applications 37.4 (July 2001), pp. 1055-1061.

## REFERENCES

[55] Kapil Venkatachalam et al. "Accurate prediction of ferrite core loss with nonsinusoidal waveforms using only Steinmetz parameters." 2002 IEEE Workshop on Computers in Power Electronics, 2002. Proceedings. IEEE. 2002, pp. 36-41.
[56] J. Muhlethaler et al. "Improved core loss calculation for magnetic components employed in power electronic system." 2011 Twenty-Sixth Annual IEEE Applied Power Electronics Conference and Exposition (APEC). Mar. 2011, pp. 1729-1736.
[57] P.L. Dowell. "Effects of eddy currents in transformer windings." Proceedings of the Institution of Electrical Engineers 113.8 (1966), p. 1387.
[58] A. Van den Bossche and V. C. Valchev. Inductors and Transformers for Power Electronics. Taylor \& Francis, Mar. 2005. URL:
https://www.crcpress.com/Inductors-and-Transformers-for-Power-Electronics/Valchev-Van-den-Bossche/p/book/9781574446791 (visited on 11/25/2016).
[59] Convection From a Rectangular Plate. http://people.csail.mit.edu/jaffer/SimRoof/Convection/.
[60] F. M. White. Viscous Fluid Flow. McGraw-Hill Higher Education, 2006.



[64] J. Taufiq. "Power Electronics Technologies for Railway Vehicles." 2007 Power Conversion Conference - Nagoya. Apr. 2007, pp. 1388-1393.
[65] N. Hugo et al. "Power electronics traction transformer." 2007 European Conference on Power Electronics and Applications. Sept. 2007, pp. 1-10.
[66] M. Steiner and H. Reinold. "Medium frequency topology in railway applications." 2007 European Conference on Power Electronics and Applications. Sept. 2007, pp. 1-10.

[68] H. Hoffmann and B. Piepenbreier. "High voltage IGBTs and medium frequency transformer in DC-DC converters for railway applications." SPEEDAM 2010. June 2010, pp. 744-749.
[69] H. Hoffmann and B. Piepenbreier. "Medium frequency transformer for rail application using new materials." 2011 1st International Electric Drives Production Conference. Sept. 2011, pp. $192-197$.
[70] Gabriel Ortiz. "High-Power DC-DC Converter Technologies for Smart Grid and Traction Applications." PhD thesis. ETHZ, 2014.

[72] G. Ortiz et al. "Design and Experimental Testing of a Resonant DC-DC Converter for Solid-State Transformers." IEEE Transactions on Power Electronics 32.10 (Oct. 2017 ), pp. $7534-7542$.

 2017 - ECCE Europe), Warsaw, Poland. 2017.

[76] Marko Mogorovic and Drazen Dujic. "100 kW, 10 kHz Medium-Frequency Transformer Design Optimization and Experimental Verification." IEEE Transactions on Power Electronics 34.2 (2019), pp. $1696-1708$.
[77] Thomas Guillod. "Modeling and Design of Medium-Frequency Transformers for Future Medium-Voltage Power Electronics Interfaces." PhD thesis. ETHZ, 2018.
[78] Group Schaffner. World's first 5 MW-DC converter. Accessed 2020.02.13. 2020. URL: https ://impulse . schaffner .com/en/worlds-first-5-mw-dc-converter.

[80] Piotr Czyz et al. "Design and experimental analysis of 166 kW medium-voltage medium-frequency air-core transformer for 1: 1-DCX applications." IEEE Journal of Emerging and Selected Topics in Power Electronics (2021).

## REFERENCES

[81] Peng Shuai. "Optimal Design of Highly Efficient, Compact and Silent Medium Frequency Transformers for Future Solid State Transformers." PhD thesis. ETHZ, 2017.
[82] Asier Garcia-Bediaga et al. "Multiobjective Optimization of Medium-Frequency Transformers for Isolated Soft-Switching Converters Using a Genetic Algorithm." IEEE Transactions on Power Electronics 32.4 (2017), pp. 2995-3006.
[83] Thomas Guillod, Panteleimon Papamanolis, and Johann W. Kolar. "Artificial Neural Network (ANN) Based Fast and Accurate Inductor Modeling and Design." IEEE Open Journal of Power Electronics 1 (2020), pp. 284-299.
[84] Irma Villar. "Multiphysical Characterization of Medium-Frequency Power Electronic Transformers." PhD thesis. EPFL, 2010.
[85] Marko Mogorovic. "Modeling and Design Optimization of Medium Frequency Transformers for Medium-Voltage High-Power Converters." PhD thesis. EPFL, 2019.
[86] Nikolina Djekanovic and Drazen Dujic. "Modeling and characterisation of natural-convection oil-based insulation for medium frequency transformers." 2022 IEEE Applied Power Electronics Conference and Exposition (APEC). 2022.
[87] Cheng Lu et al. "AC Resistance Calculation Method for Hollow Conductor Windings in High Power Medium Frequency Transformers." CSEE 36.23 (2016)
[88] Nikolina Djekanovic and Drazen Dujic. "Design Optimization of a MW-level Medium Frequency Transformer." PCIM Europe 2022. 2022, pp. 1-10.
[89] Hitachi Metals Ltd. Japan.https://www.hitachi-metals.co.jp/e/.URL:https://www.hitachi-metals.co.jp/e/.
[90] Luvata Pori Oy, Finland. https://www.luvata.com/. URL: https://www.luvata.com/.
[91] Elektro-ISola A/S, Denmark. https://www.elektro-isola.com/. URL: https ://www. elektro-isola . com/.
[92] Midel 7131.https://www.midel.com/. URL: https://www.midel.com/
[93] Renan Pillon Barcelos and Dražen Dujić. "Nodal Impedance Assessment in DC Power Distribution Networks." 2021 IEEE 22nd Workshop on Control and Modelling of Power Electronics (COMPEL). 2021, pp. 1-8.
[94] Renan Pillon Barcelos and Drazen Dujic. "Direct Current Transformer Impact on the DC Power Distribution Networks." IEEE Transactions on Smart Grid 13.4 (2022), pp. 2547-2556.

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## Tutorial pdf can be downloaded from:

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[^0]:    - PEL Medium Voltage Laboratory

[^1]:    - Reverse conducting IGCT structure and symbol

[^2]:    - SOFTGATE no load operation

[^3]:    - SOFTGATE continuous operation

[^4]:    41] Jakub Kucka and Drazen Dujic. "Shoot-Through Protection for an IGCT-Based ZVS Resonant DC Transformer." IEEE Transactions on Industrial Electronics (2022), pp. 1-1

[^5]:    Comparison of switching energy (top), voltage rise time (middle) and $\Delta V_{\text {dyn }}$ (bottom) during turn-off as a function of $I_{\text {off }}$ and for indicated snubber capacitances. o Standard, $0+55 \%$ - irradiated, and $0+95 \%$ irradiated devices.

[^6]:    - H and J distribution within the core window area.

[^7]:    A All modes of heat transfer are present. Which one is dominant is the matter of design choices.

